

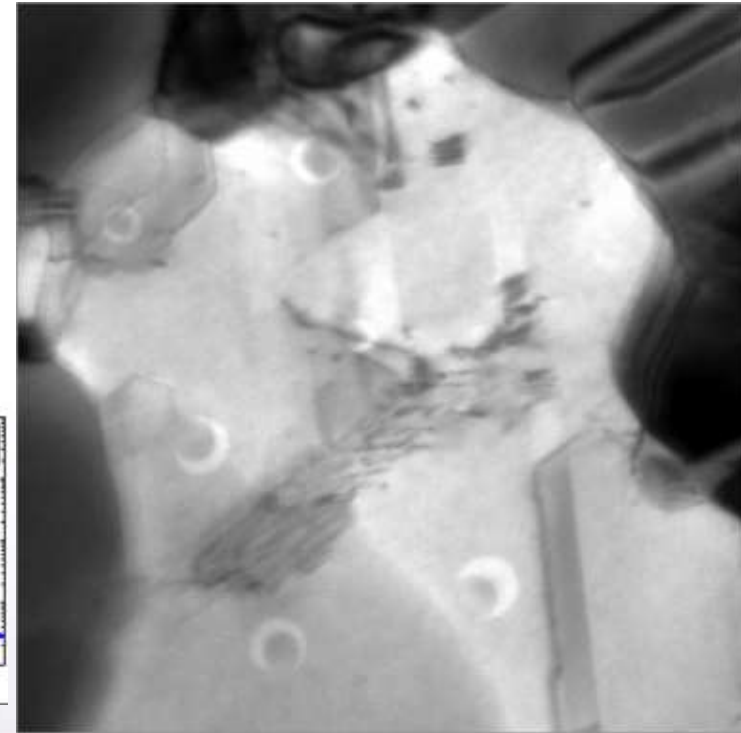
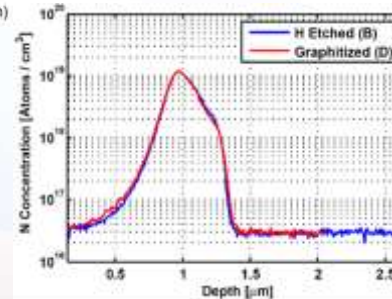
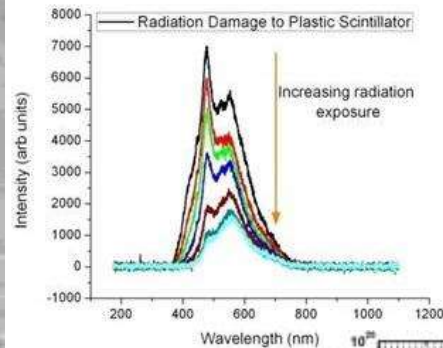
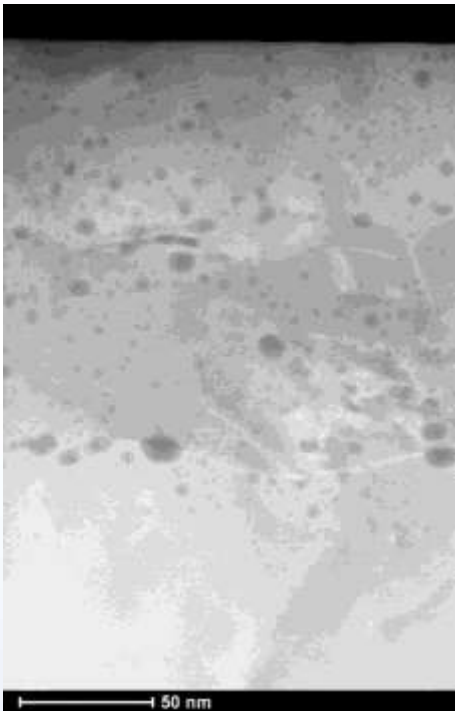
# Tailoring Nanostructures via Ion Beam Modification

SAND2013-9595C

K. Hattar

Sandia National Laboratories

November 6, 2013



## Collaborators:

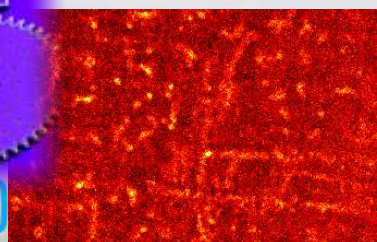
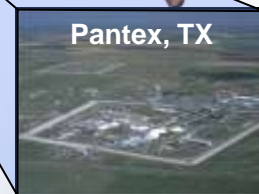
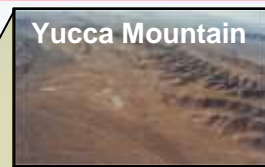
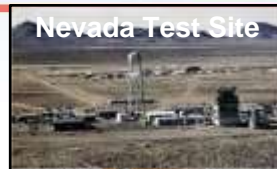
- IBL: D. Buller, S.B. Van Deusen, B.G. Clark, B.L. Doyle, S.M. Hoppe, S. Rajasekhara, J. Villone, G. Vizkelethy
- Sandia: T.E. Buchheit, B. Boyce, T.J. Boyle, F.P. Doty, P. Feng, S. Goods, B.A. Hernandez-Sanchez, A.C. Kilgo, P.G. Kotula, J. Puskar, M.J. Rye, J.A. Scott, P. Yang
- External: L.N. Brewer, S. Maloy, A. McGinnis, P. Rossi, D. Masiel, D. Gross, J. Kacher, I.M. Robertson, & Protochips Inc.



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# Sandia National Laboratories

*"Exceptional service in the national interest"*

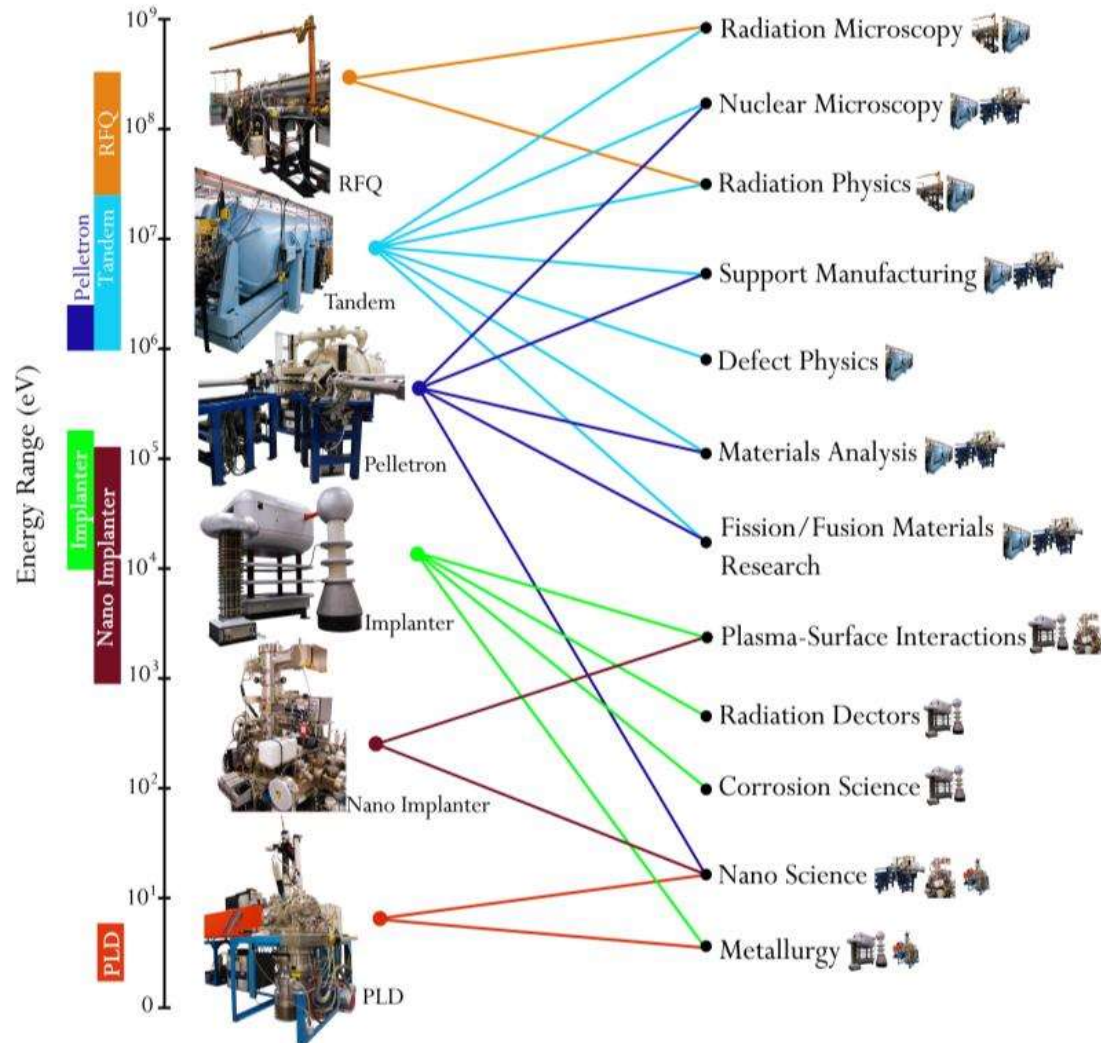


# Sandia's New Ion Beam Lab



A special 72 wheeled vehicle with independent steering for each pair of wheels was used to move the Tandem accelerator

## Ion Beam Laboratory Capabilities

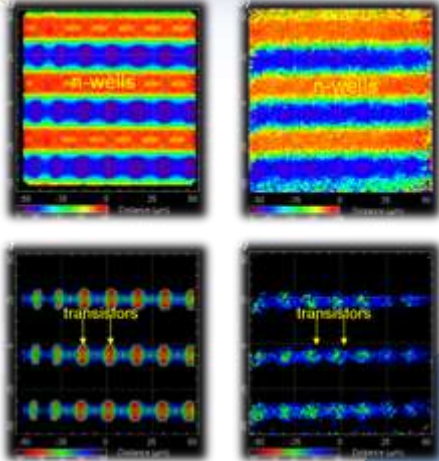


**New Facility**  
 laboratory space  
 1850 m<sup>2</sup>  
 office space  
 650 m<sup>2</sup>  
**Old Facility:**  
 1300 m<sup>2</sup> total

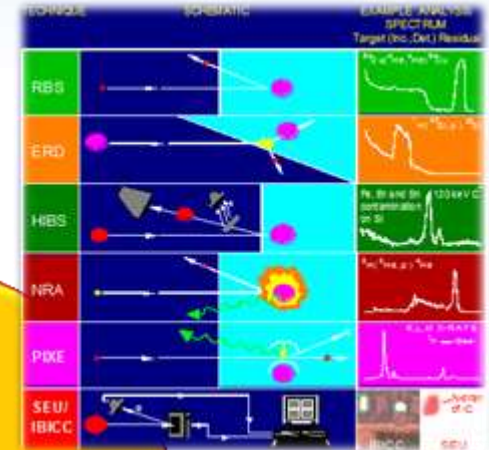
**Building: \$20M**  
**Equipment: \$11M**  
**Total: \$40M**



# Sandia's Ion Beam Laboratory



Ion Beam Analysis (IBA)

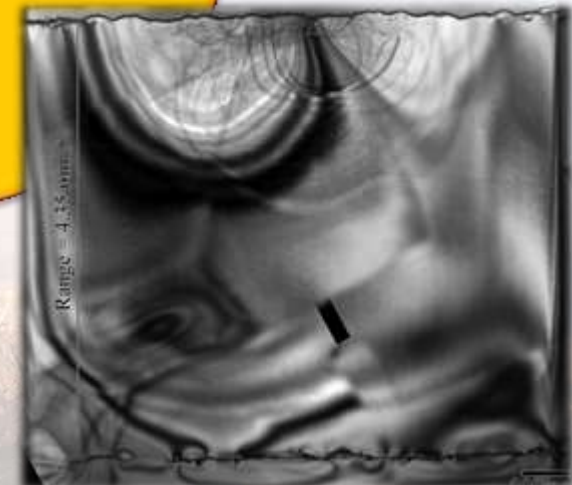


Radiation Effects Microscopy (REM)



Ion Beam Modification (IBM)

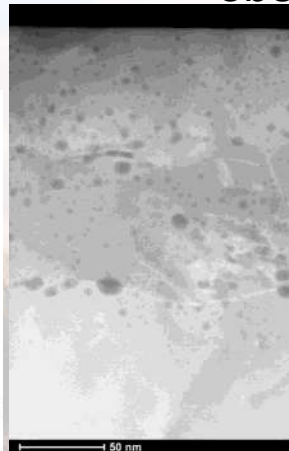
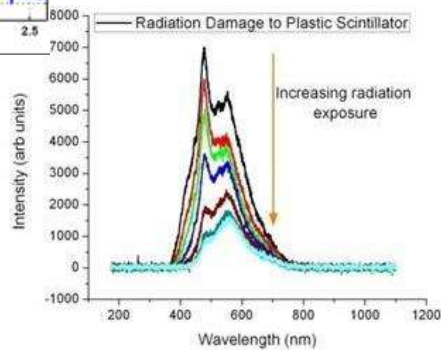
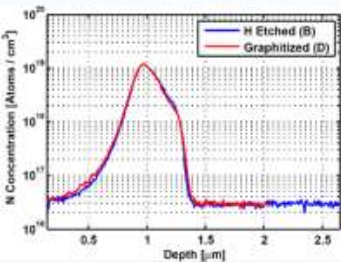
*In situ* Ion Irradiation Transmission Electron Microscopy (I<sup>3</sup>TEM)



# Outline

## 1. Materials Engineering

- Control of Local Chemistry
  - ♦ Development of back gates for graphene devices
- Investigate Radiation Tolerance
  - ♦ Various radiation detectors from MOFs to complex oxides
- Control of Local Structure
  - ♦ Improving the wear properties of electrical contacts



## 2. Materials Science

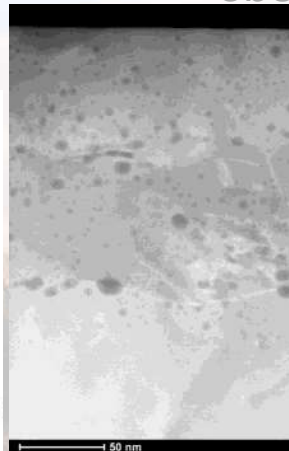
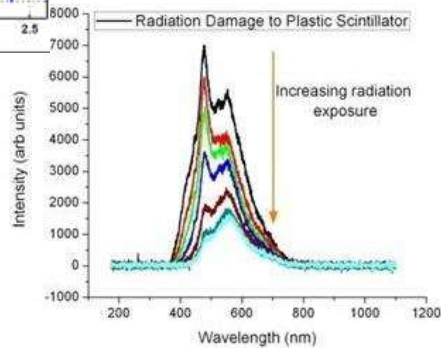
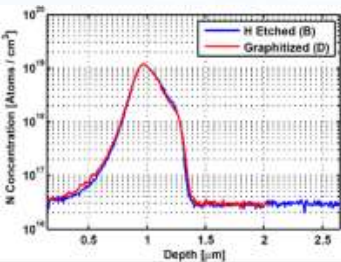
- Broad Capability of the I<sup>3</sup>TEM
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- Revisit of the Structural Control
  - ♦ In-situ study of Au electrode evolution under ion beam modification
  - ♦ Initial work on indentation and cyclic compression
- Fun future directions for real-time nanoscale observation in extreme environments



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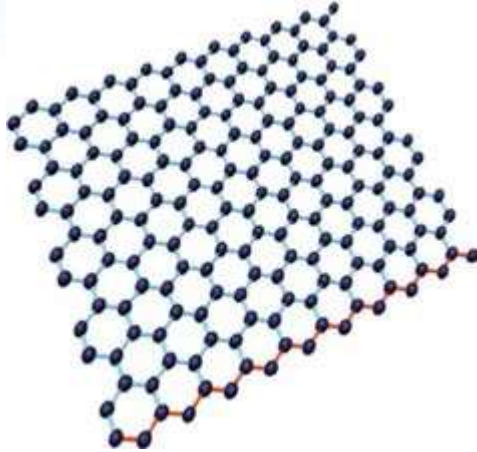


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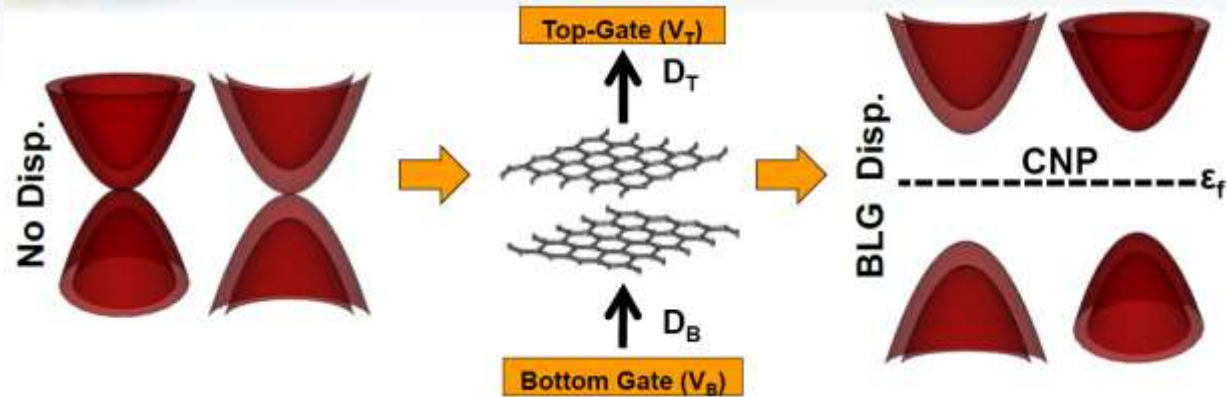
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# Development of a Dual-Gated Bilayer Graphene Device



2D hexagonal net of  $sp^2$  bonded carbon atoms



**A combination of displacements (top & bottom gates) are needed to:**

- Induce a bandgap
  - $D_{ave} \neq 0$
- Control Fermi Level ( $\epsilon_f$ ) to charge neutrality point (CNP)
  - $\delta D = 0$

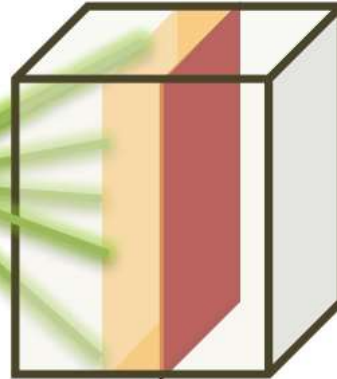


# 3 MeV Nitrogen Implants to Form a Back-Gate in Semi-Insulating SiC

3 MV NEC  
Pelletron

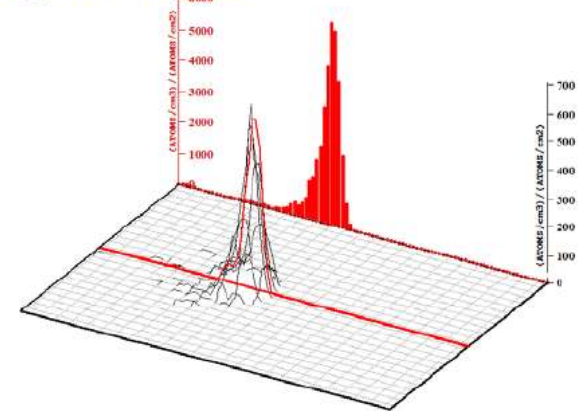


SiC  
Sample



TRIM Simulation of Blanket  
Implant Depth Distribution

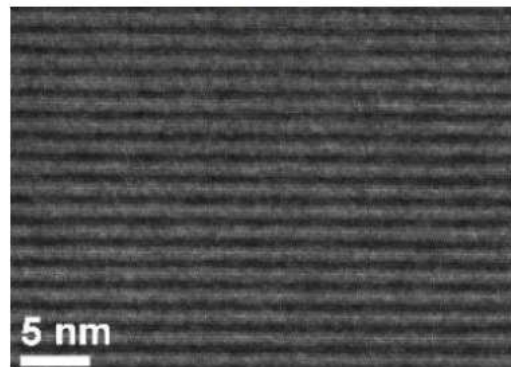
Ion Range = 1.90  $\mu\text{m}$  Skewness = -2.803  
Straggle = 871  $\text{\AA}$  Kurtosis = 18.530



## Ion Implantation Results

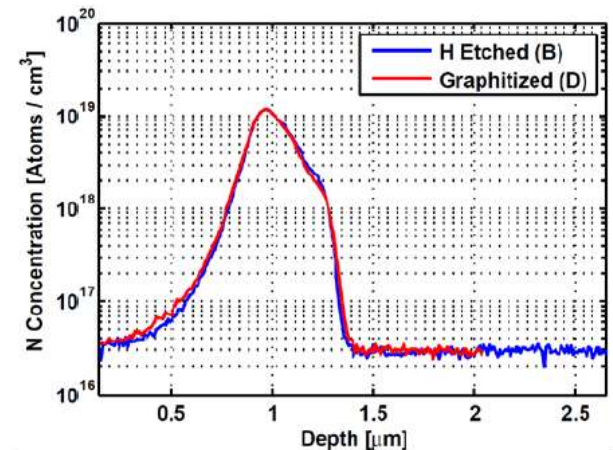
- Implanted N ions (target depth of 1  $\mu\text{m}$ )
- Capacitance measurements indicated an isolated conductive layer at a depth of  $\sim 700$  nm in the SiC

TEM Validation of  
Microstructure



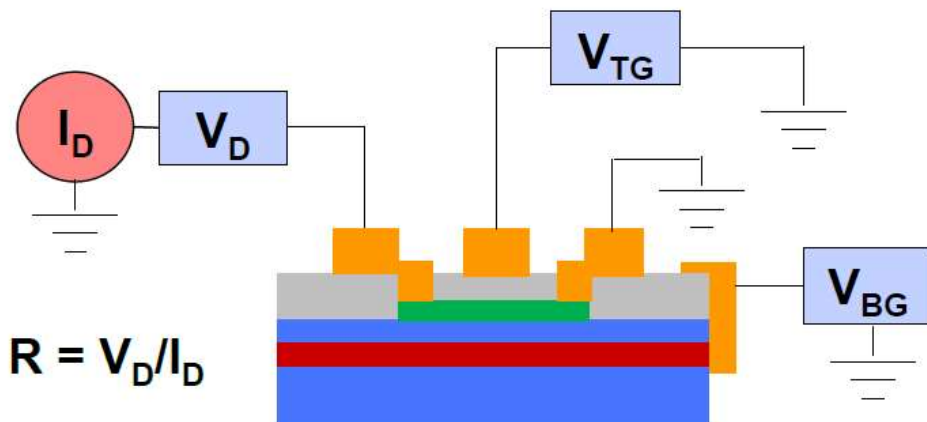
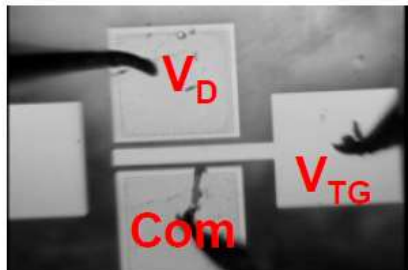
Tailored ion implantation  
provides both back gate  
and side contact structure

Validation of Implant Depth (SIMS)

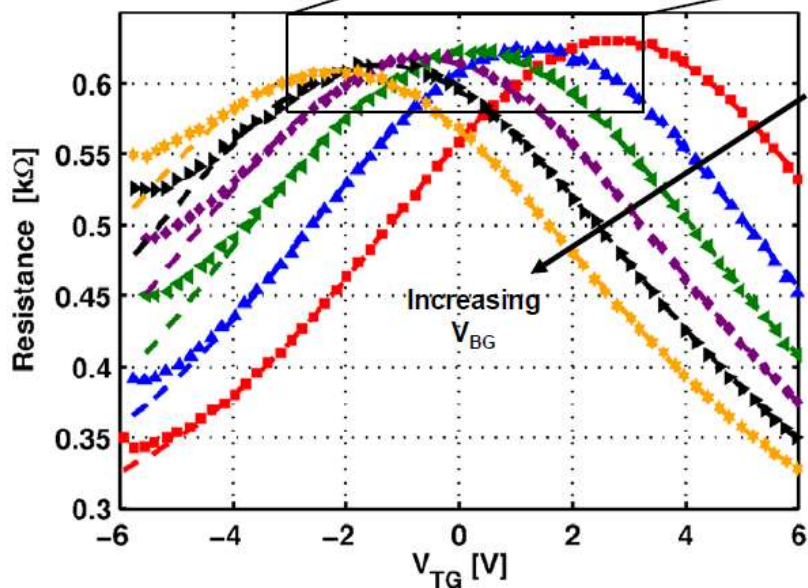
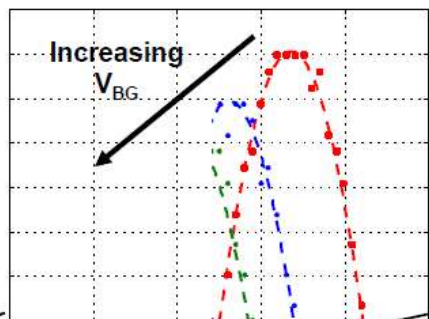


# Bandgap Control via Dual Gating

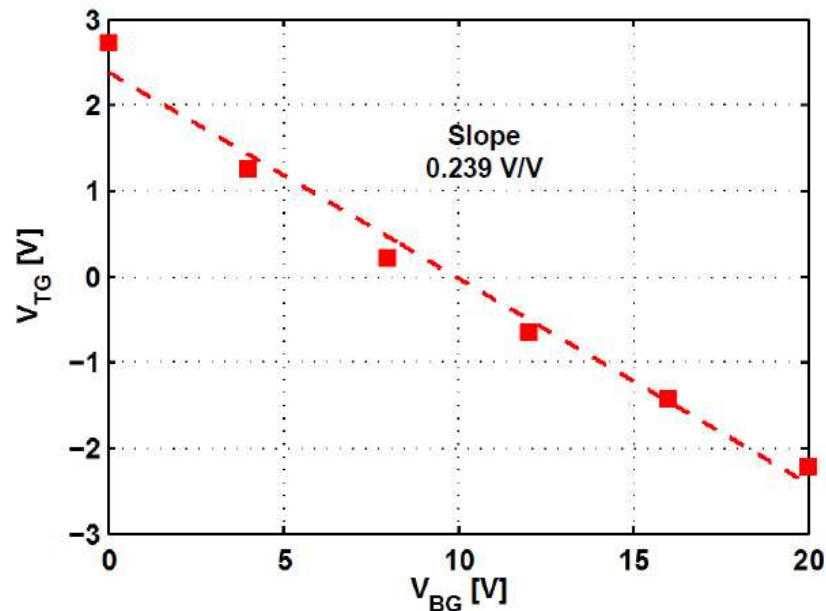
(1<sup>st</sup> Demonstration of scalable dual-gate BLG FETs)



$V_{BG} = 0\text{ V to }20\text{ V}$   
in 4 V Steps



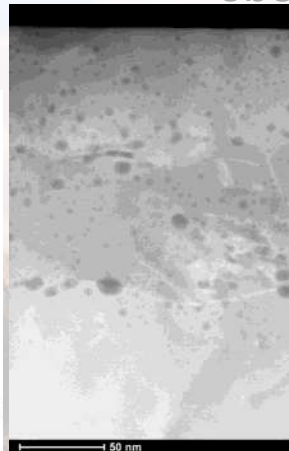
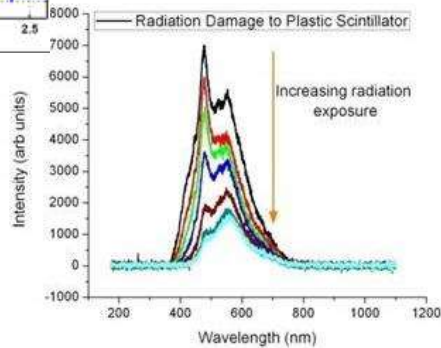
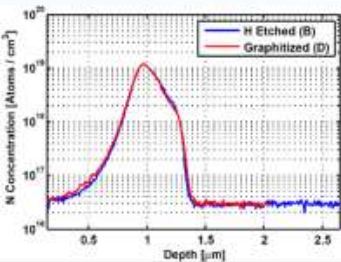
$$\text{Slope} = -(\epsilon_b d_t)/(\epsilon_t d_b)$$



# Outline

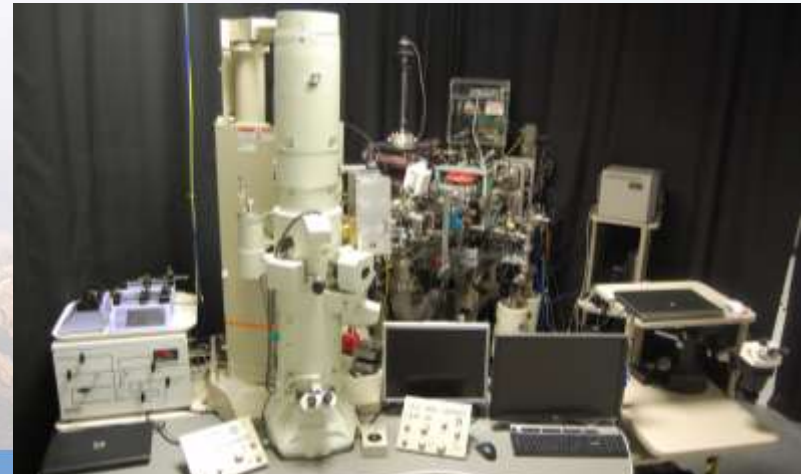
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# Interest in Scintillators

Crucial to understand radiation-solid interactions on multiple length scales

Plastic Scintillators



Single Crystal CdWO<sub>4</sub>



Non-Interpenetrated IRMOF-10



US Ports: 2 Billion Metric Tons

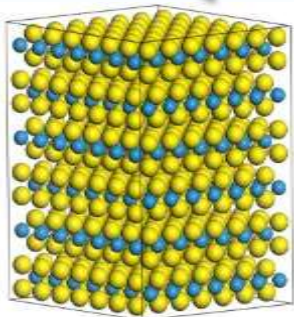


Scintillators with low energy resolution & detection efficiency cannot distinguish radiation type or quantify radiation

Nano

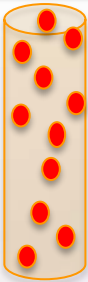
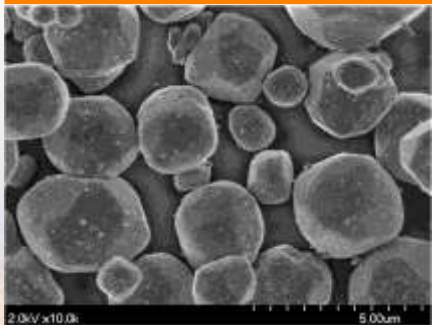
Micro

Meso



Tungsten (IV) Sulfide WS<sub>2</sub>

Commercial CaWO<sub>4</sub> Scintillating Powder



High-Z Nanocomposite

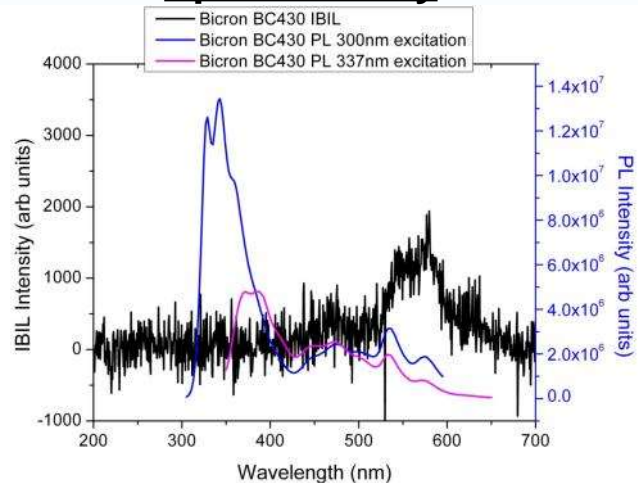


High-Z ME<sub>x</sub> Nanoscintillator

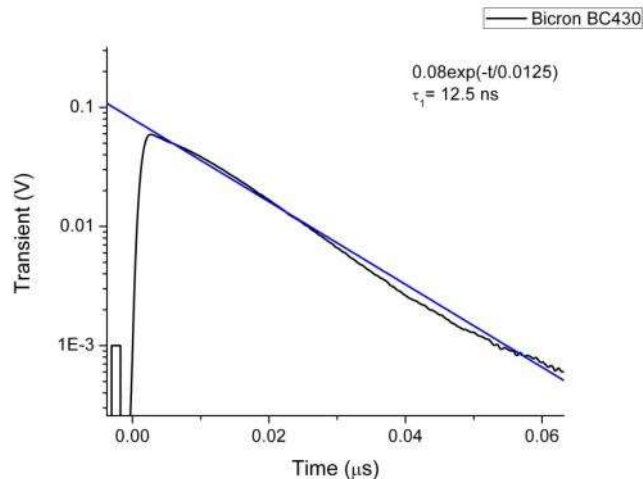
# IBL Capabilities for Luminescence Studies

Collaborators: J. Villone & G. Vizkelethy

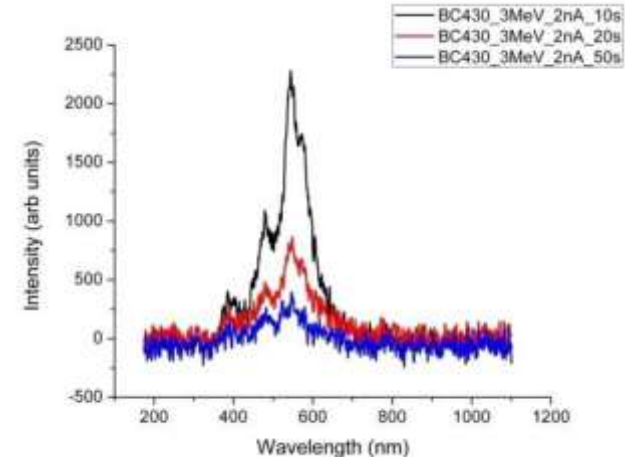
## Spectrometry



## Decay Time



## Radiation Hardness



### 3 MeV H<sup>+</sup> beam

- Thin films of samples on PIN diodes
- Hamamatsu PMT run in photon-counting mode
- Light intensity measured as a function of time after ion strike

### 3 MeV H<sup>+</sup> beam used as excitation

- Scintillation light collected as ion beam excites sample
- Light collected with OM-40 microscope or fiber optic mounted close to sample
- Avantes AvaSpec 2048 spectrometer

### Radiation hardness experiments performed with 3 MeV H<sup>+</sup> beam from Tandem accelerator

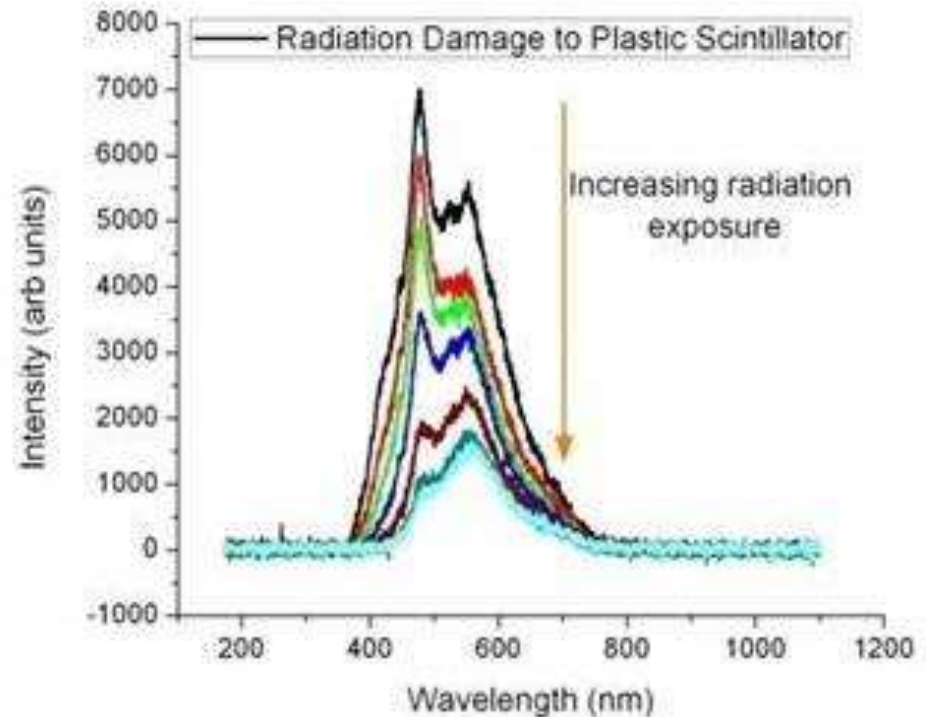
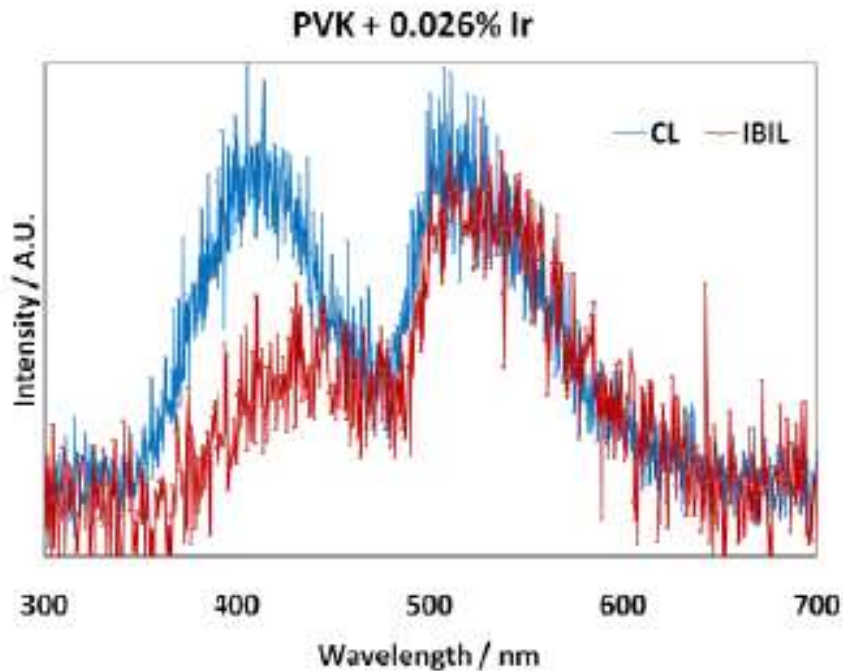
- IBIL spectra measured constantly as sample exposed to beam
- Overall decrease in emitted light observed due to radiation damage



# IBIL of MOFs

Collaborators: P. Feng, F.P. Doty, & J. Villone

*Metal-organic frameworks demonstrate spectral discrimination with IBIL/CL*



▣ Spectral discrimination

▣ CL simulates response to gamma rays

▣ IBIL simulates response to neutrons

▣ PL and IBIL of MOF demonstrating spectral discrimination

▣ IBIL decay of MOFs with irradiation – changes observed in relative peak height

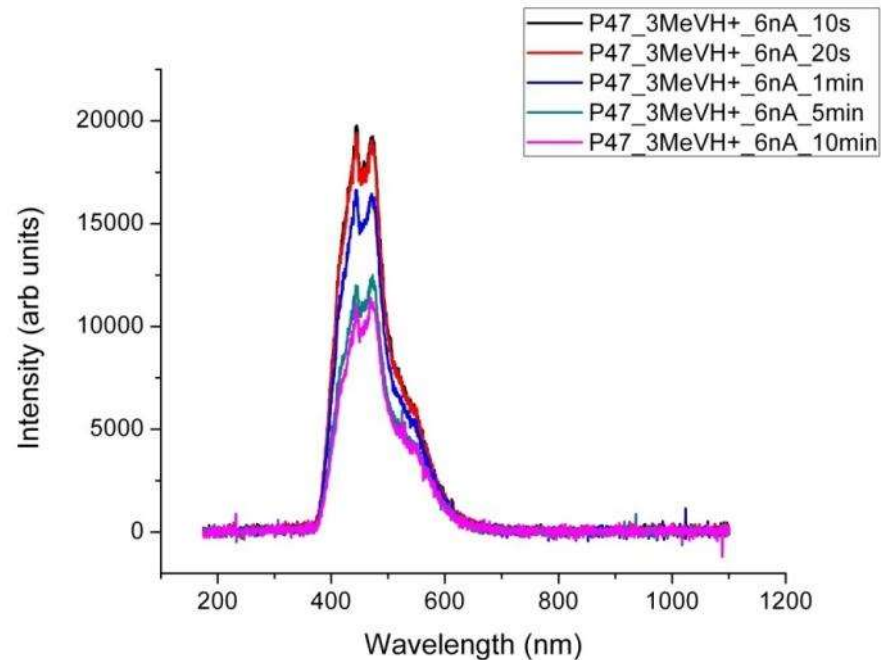
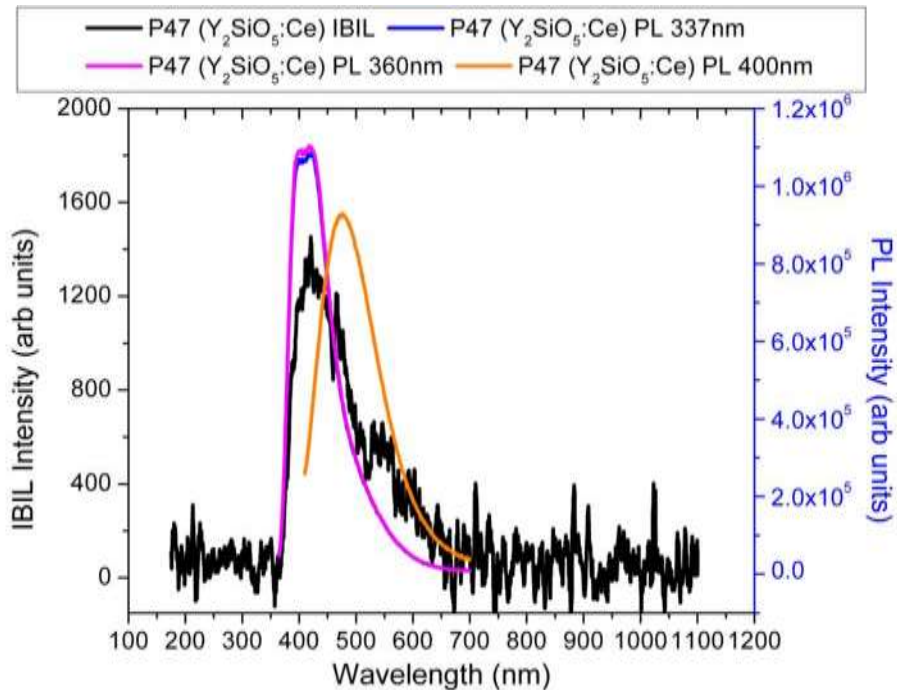


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# IBIL of Oxides

Collaborators: J. Villone & G. Vizkelethy

*P47 phosphor studied for potential in radiation effects microscopy*



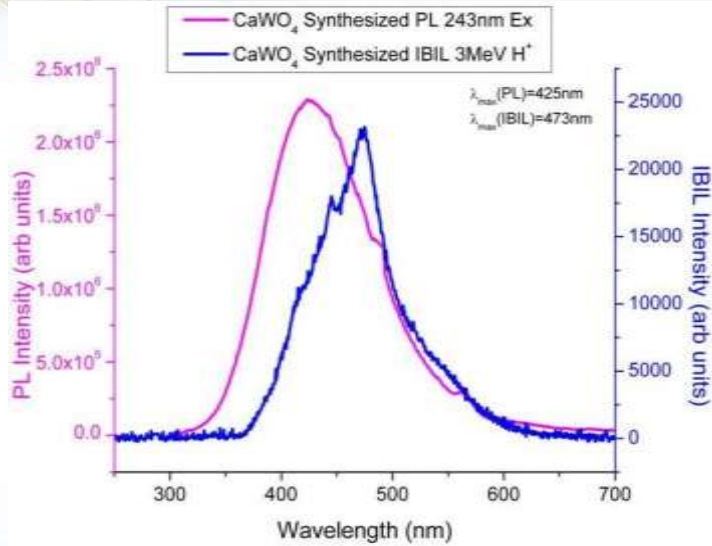
- ▣ P47 is effective phosphor – PL and IBIL similar
- ▣ Peak emission dependent on excitation wavelength

- ▣ Degradation in optical properties also observed in P47
- ▣ Oxides demonstrate improved radiation tolerance compared to organic scintillators

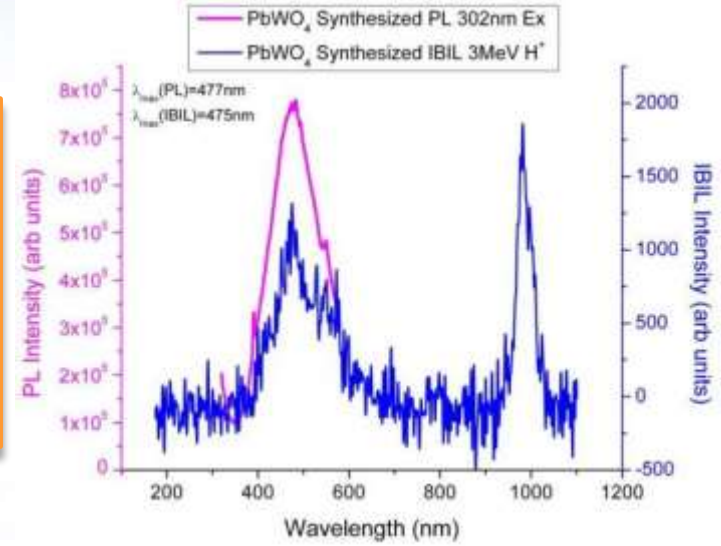


# IBIL of Nanoscintillators

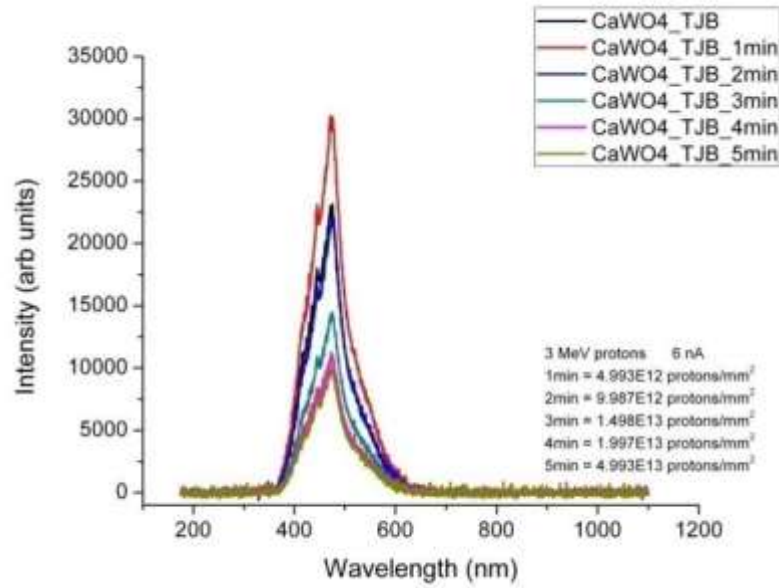
Collaborators: B.A. Hernandez-Sanchez, S.M. Hoppe, T.J. Boyle, J. Villone & P. Yang



Luminescence with proton excitation demonstrates different properties than with UV excitation



Crucial to study materials with various excitation mechanisms to fully understand luminescent properties



Most materials demonstrate a degradation in optical properties with irradiation – want to understand fundamental mechanism



# Results - Nanoscintillators

Collaborators: B.A. Hernandez-Sanchez, S.M. Hoppe, T.J. Boyle, J. Villone & P. Yang

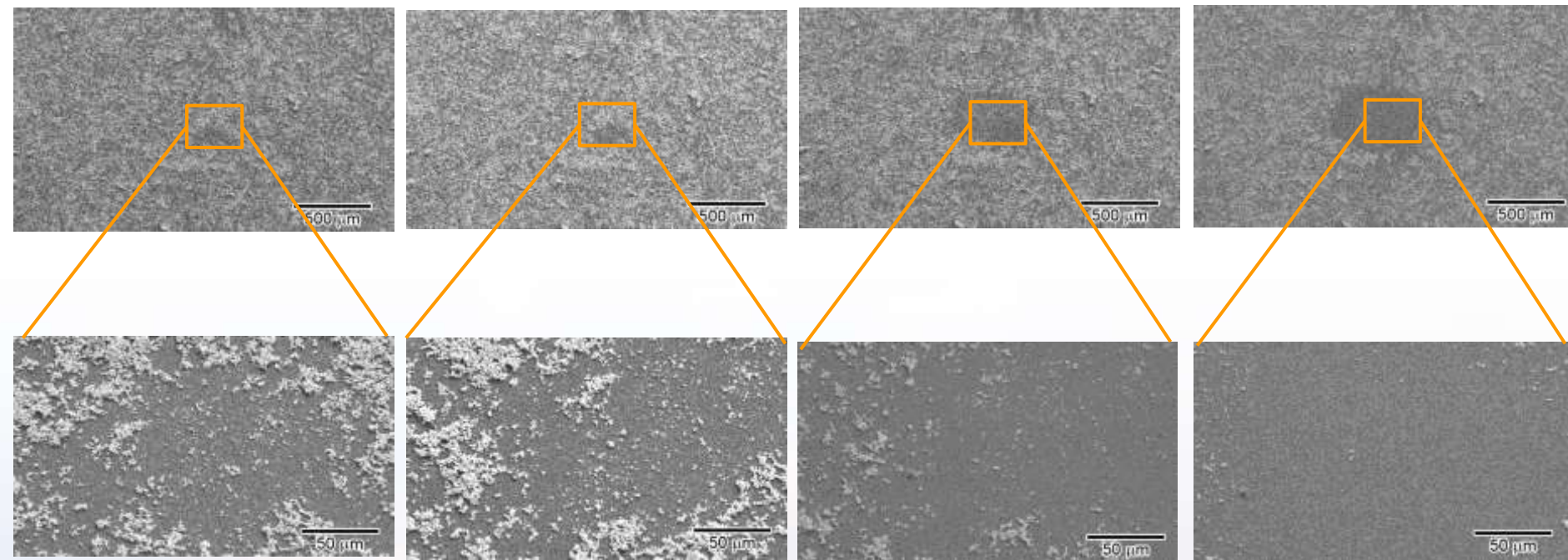
## Nearly In-situ SEM Ion Irradiation of Nanoscintillators

As deposited Nanoparticles

3 MeV H<sup>+</sup> 7 nA 1 sec

3 MeV H<sup>+</sup> 7 nA 5 sec

3 MeV H<sup>+</sup> 7 nA 30 sec



- Drop cast films of PbWO<sub>4</sub> nanoscintillators irradiated with 3 MeV H<sup>+</sup> beam, then imaged with SEM
- Material being ablated off of the surface – need better technique to study microstructural changes

Can we understand how the microstructure is affected by irradiation?  
How does the influences effect optical properties?

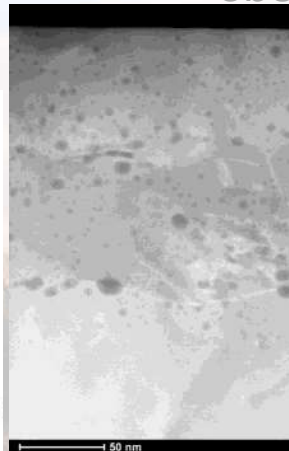
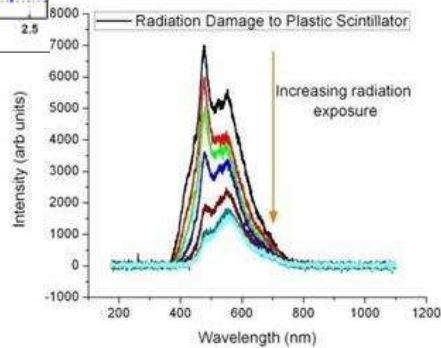
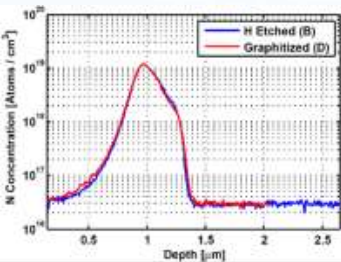


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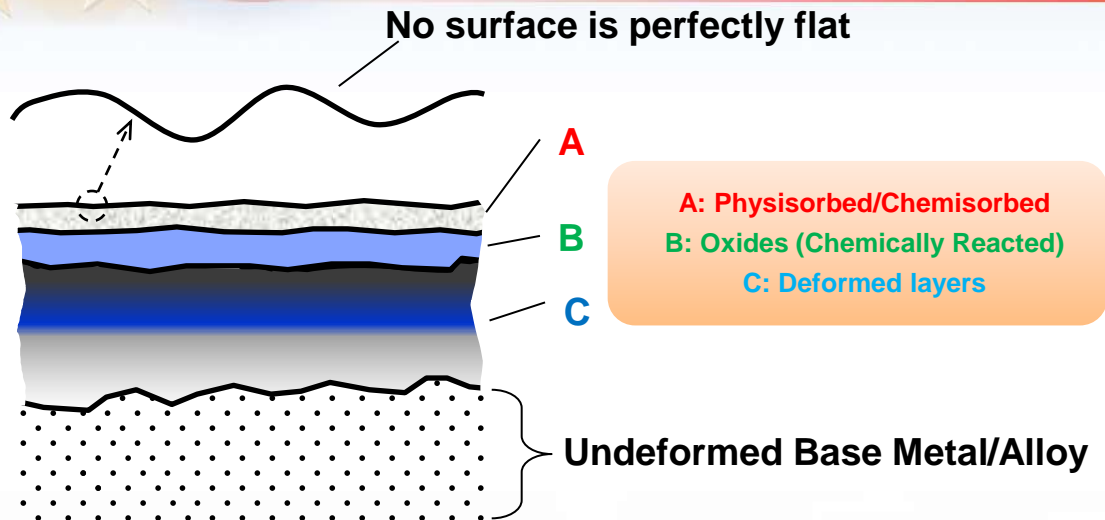


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# Nature of Metallic Surfaces

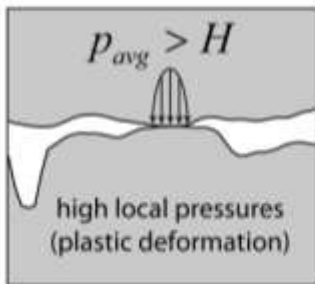


*Real area of contact ( $A_r$ ) to be minimized for low adhesion (Low Adhesive Wear)*

*Or maximized for reduced electrical contact resistance (ECR)*

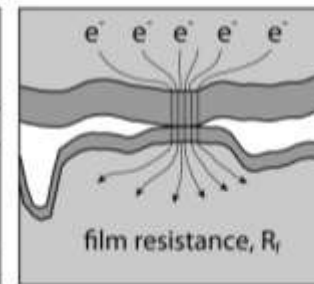
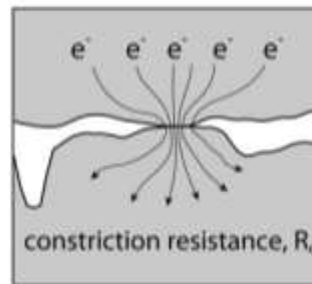
## Asperity Contacts, Constriction, Asperity Contacts and Surface Films

areal sum of asperity contacts and surface films define electrical contact resistance



... for metal contacts the real area is a function of hardness and contact force (Bowden & Tabor, 1939):

$$A_r \cong \frac{F_n}{H}$$



... ECR is a function of the constriction and film resistances:

$$ECR = \sum_i (R_{c,i} + R_{f,i})$$

Archard, *Journal of Applied Physics* (1953) 24:981

R. Holm, *Electrical Contacts Handbook* (1958) Berlin: Springer-Verlag

Greenwood & Williamson, *Proc. Royal Society* (1966) A295:300

T.W. Scharf & S.V. Prasad, *Journal of Material Science* (2013) 48:511-531

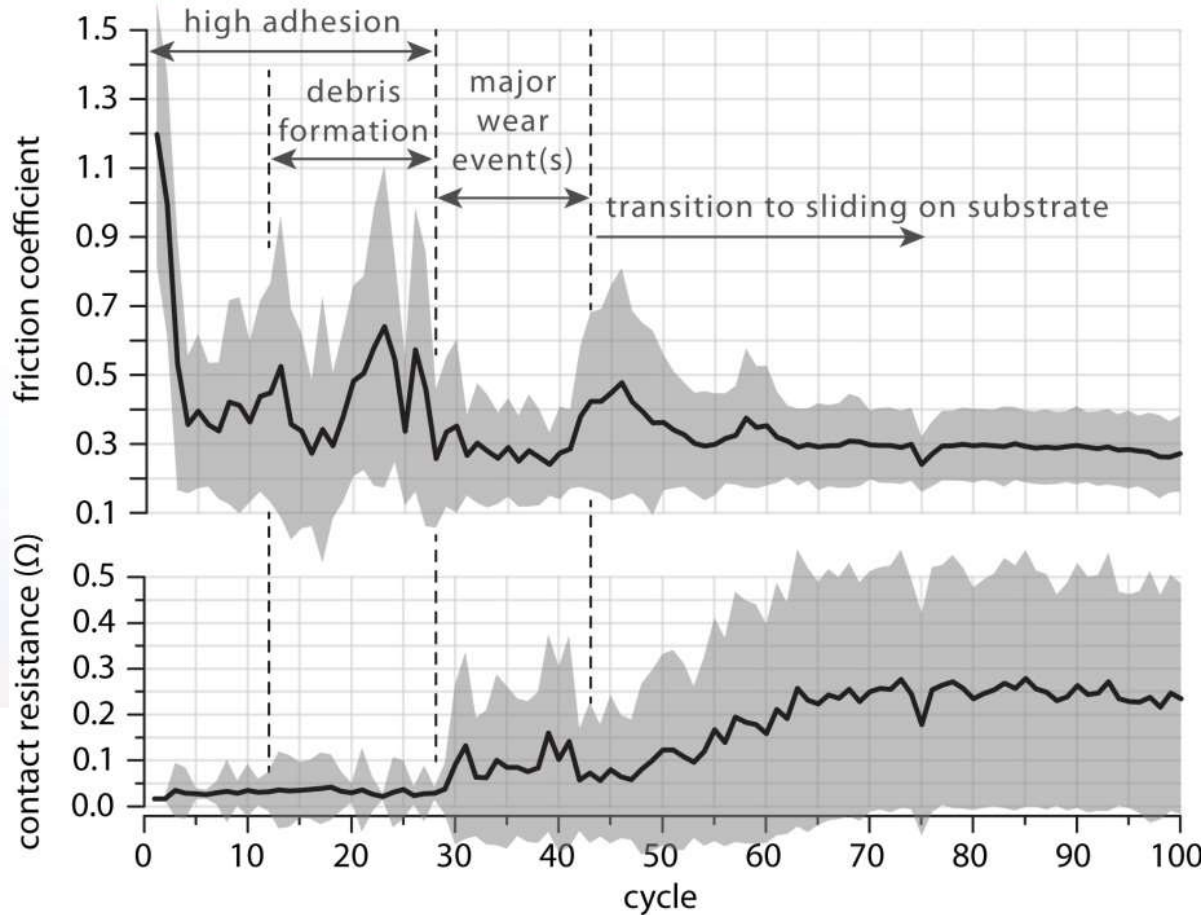


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# ECR-Friction Behavior of Pure Au



## pure Au film sliding against Neyoro G

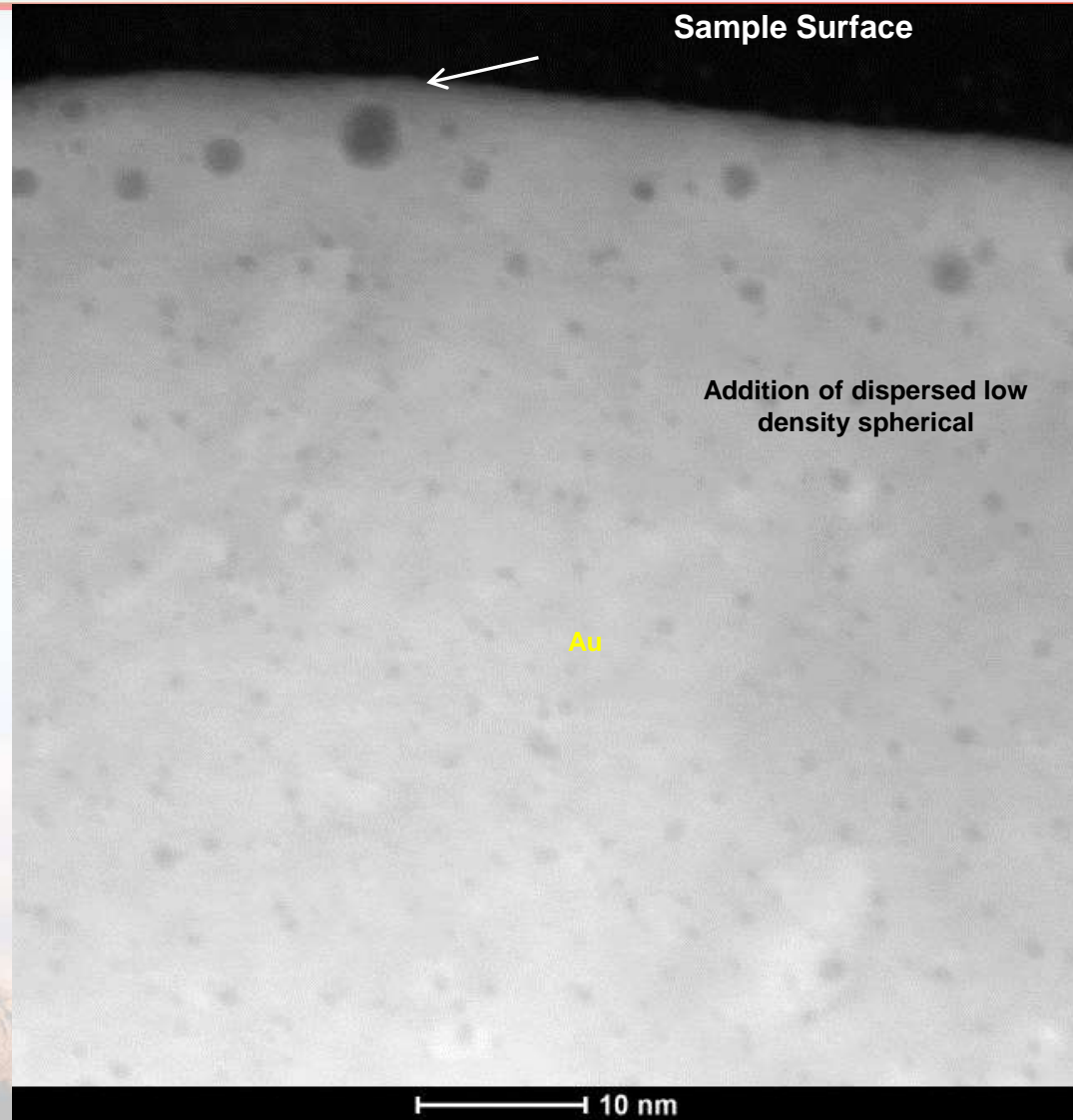


- Neyoro G (Au-Cu),  $\frac{1}{16}$  in. radius hemispherical tip rider
- $F_n = 100$  mN ( $\approx 290$  MPa contact stress)
  - 100 Cycles @  $v = 1$  mm/s
- 1 – 2 mV bias to achieve approximately 100 mA
- Lab air environment at room temperature

# Modeling and STEM of He Implantation

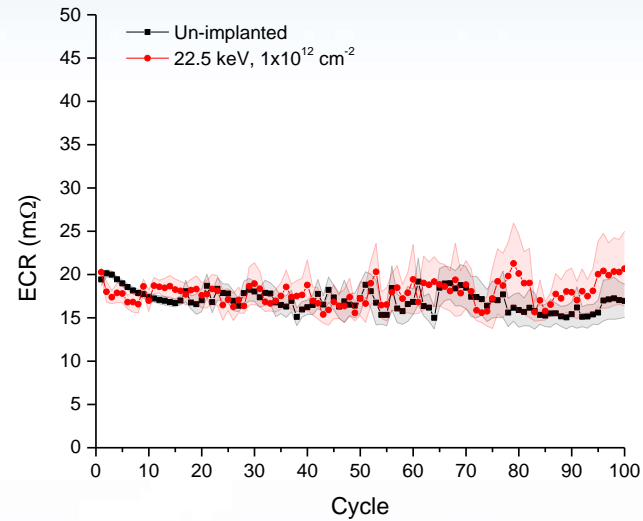
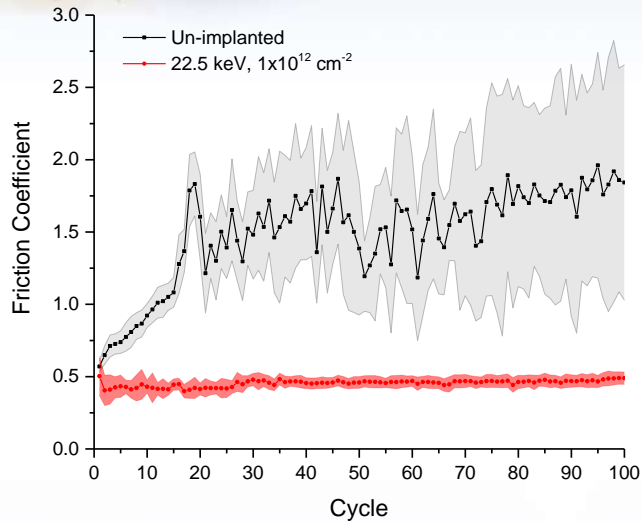
22.5 keV He Ions

- Simulations: SRIM 2008 (The Stopping and Range of Ions in Matter, J.F. Ziegler, M.D. Ziegler and J.P. Biersack)
  - Monte-Carlo simulation of kinematic interaction based on empirical data fitted functions
  - Input variables of target material include density, AMU, and thickness.
  - Input variables of ions include AMU, energy, and angle of incidence.
  - Assumes isotropic material, thus no consideration for channeling effects
- AC-STEM used to observe the distribution of implanted bubbles
- Bubble locations are in good agreement with SRIM ion range predictions



*He implantation result in small dispersed spherical structures assumed to be He bubbles.  
Dispersion and depth can be tailored*

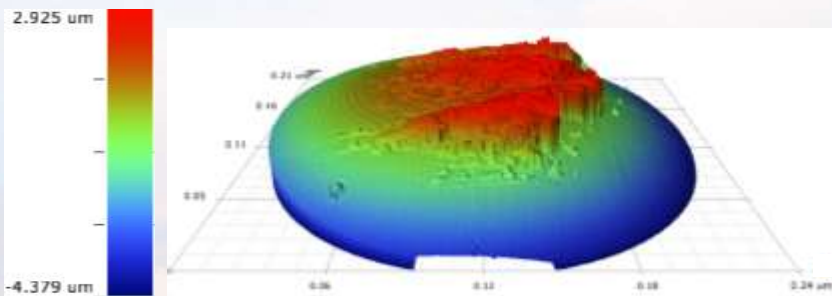
# ECR and Wear Measurements



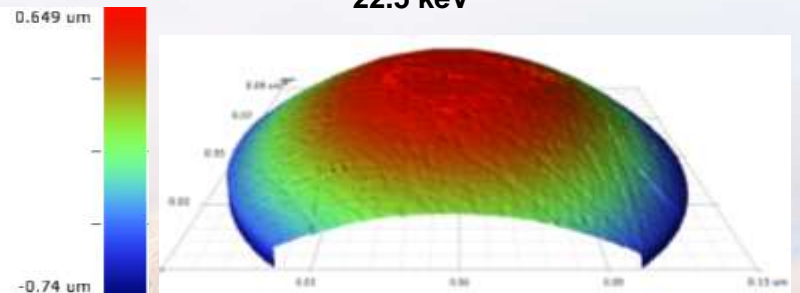
**Friction is significantly reduced with <sup>3</sup>He implantation while maintaining ECR performance**

**Scanning white light interferometer topographical construction of riders after 100 cycles**

Rider after 100 cycles against Un-implanted Au



Rider after 100 Cycles against Au implanted to 1E12 cm<sup>-2</sup> @ 22.5 keV



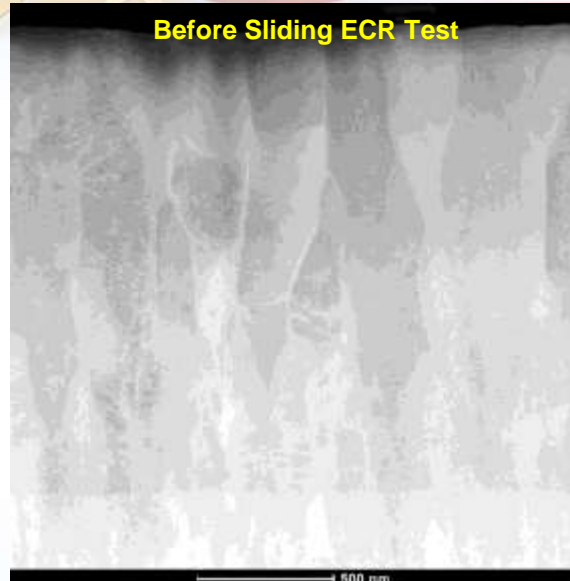
***Wear is significantly reduced with minimal effect in ECR***



# STEM Images of Sub-surfaces

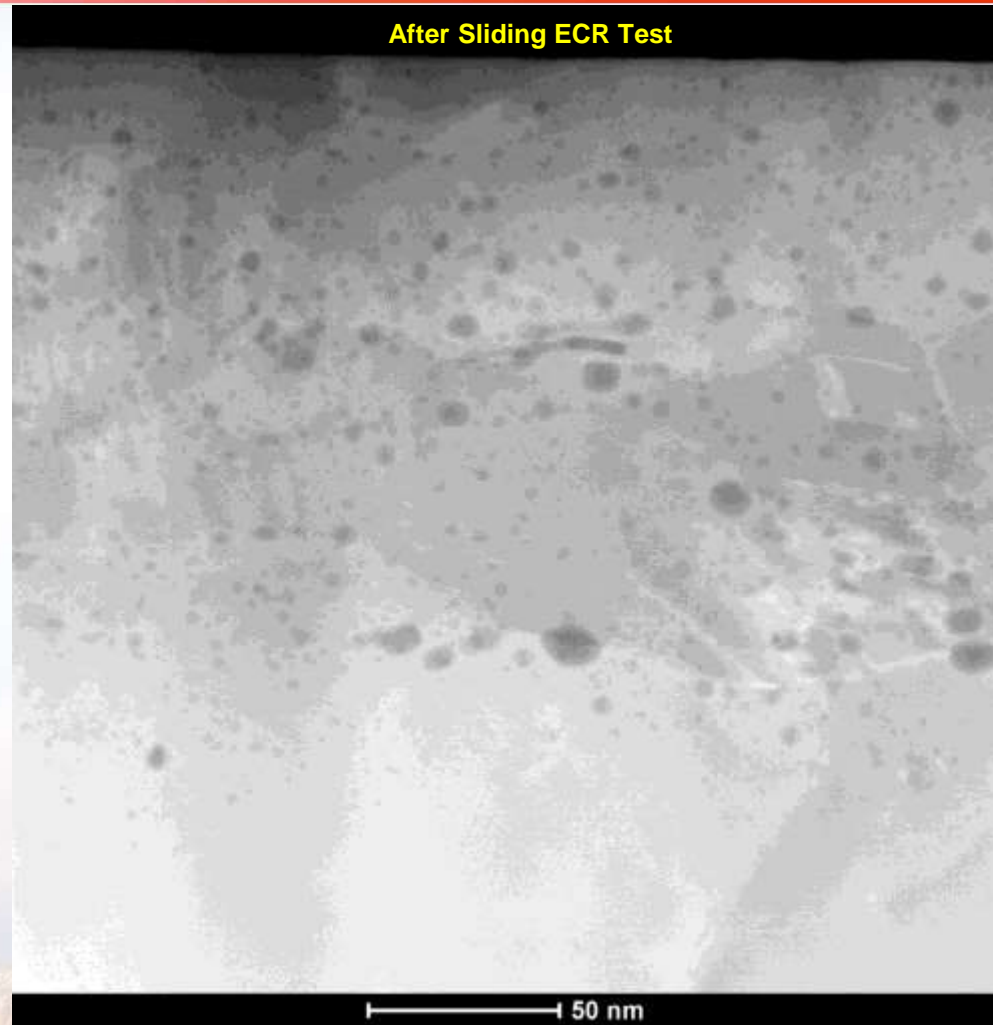
22.5 keV,  $1 \times 10^{12} \text{ cm}^{-2}$

Before Sliding ECR Test

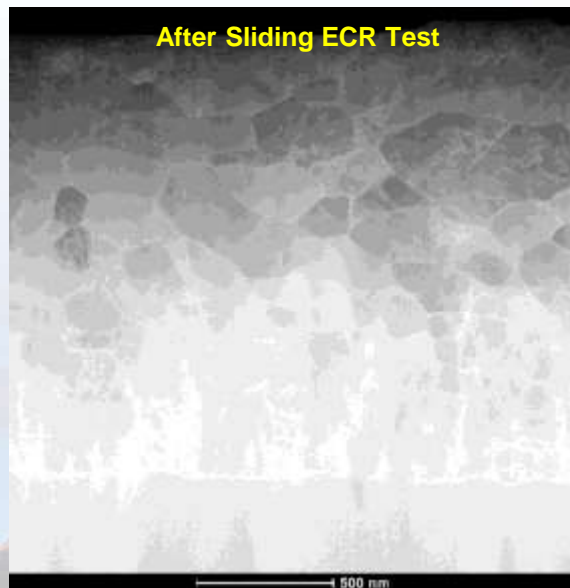


*Recrystallization  
is observable  
after 100 cycles*

After Sliding ECR Test



After Sliding ECR Test



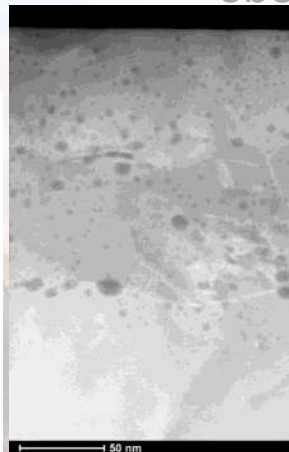
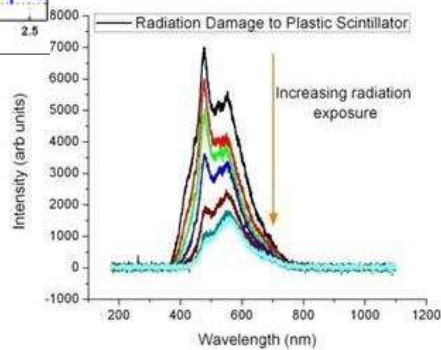
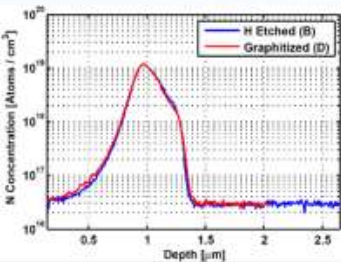
**Au – Pt  
Interface**

*An increase in both observable density and diameter of He bubbles,  
suggests wear induced He coalescence from interstitial and previously  
un-observable He*

# Outline

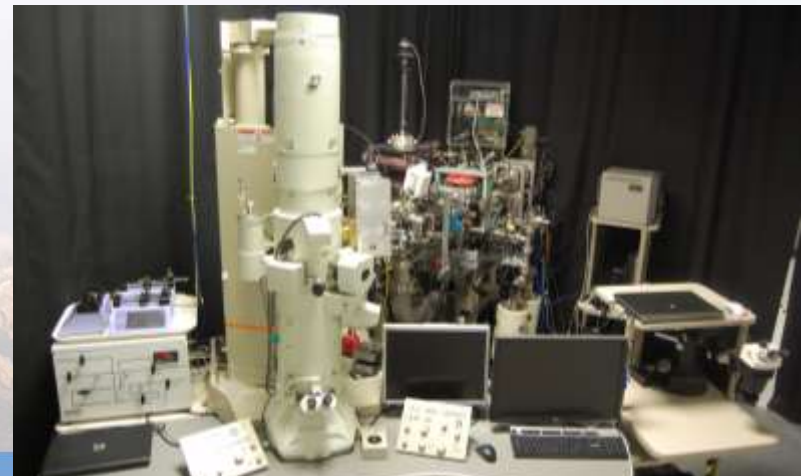
## 1. Materials Engineering

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- Investigate Radiation Tolerance
  - ♦ Various radiation detectors from MOFs to complex oxides
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## 2. Materials Science

- Broad Capability of the I<sup>3</sup>TEM
- Revisit of the Radiation Detectors
  - ♦ In-situ ion irradiation of high-z nanoscintillators
- Revisit of the Structural Control
  - ♦ In-situ study of Au electrode evolution under ion beam modification
  - ♦ Initial work on indentation and cyclic compression
- Fun future directions for real-time nanoscale observation in extreme environments



# Benefits & Limitations of *in situ* TEM

## Benefits

1. Real-time nanoscale resolution observations of microstructural dynamics

## Limitations

1. Predominantly limited to microstructural characterization
  - Some work in thermal, optical, and mechanical properties
2. Limited to electron transparent films
  - Can often prefer surface mechanisms to bulk mechanisms
  - Local stresses state in the sample is difficult to predict
3. Electron beam effects
  - Radiolysis and Knock-on Damage
4. vacuum conditions
  - $10^{-7}$  Torr limits gas and liquid experiments feasibility
5. Local probing
  - Portions of the world study is small

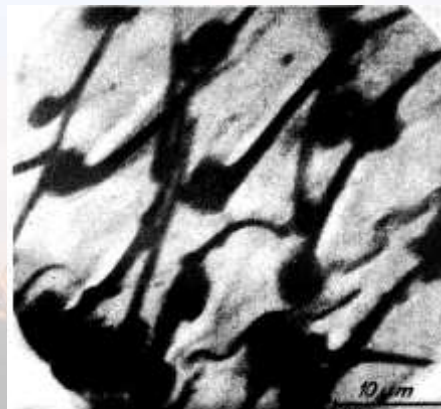


Fig. 1: Micro section of the lenses (E) (From internal photograph; U = 60 kV; M<sub>x</sub> = 2200) (Dietz, E. and Maier, H.O. Z. Wiss. Mikroskopie 32, 85-97 (1995))

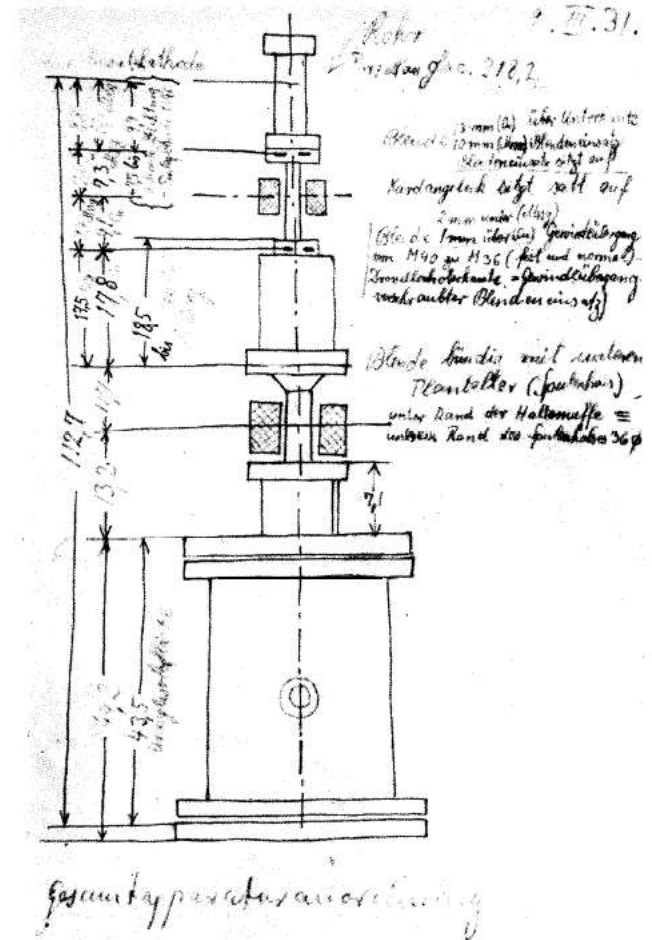
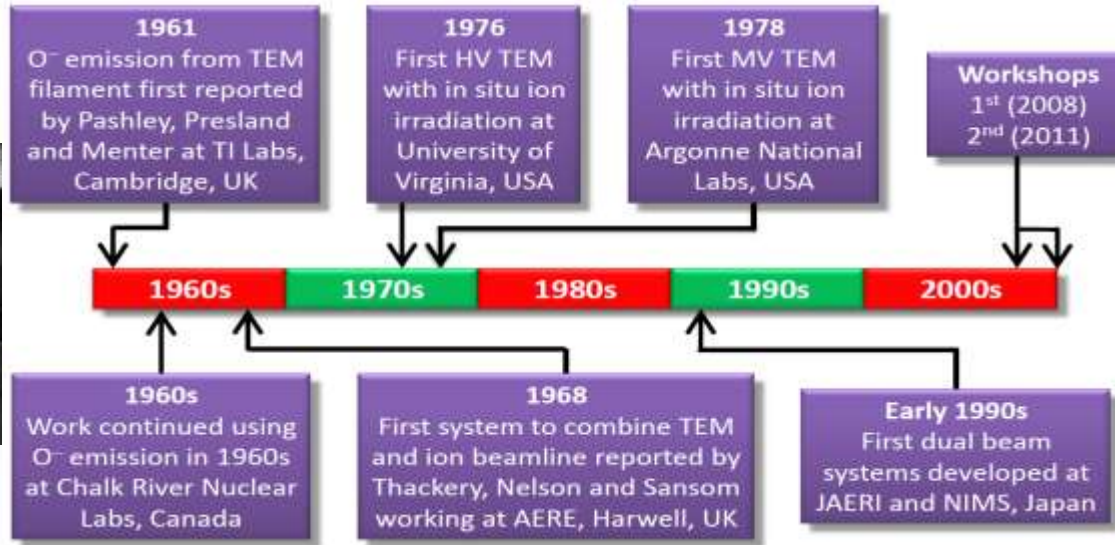


Fig. 2: Sketch by the author (9 March 1931) of the cathode ray tube for testing one-stage and two-stage electron-optical imaging by means of two magnetic electron lenses (electron microscope) [8].



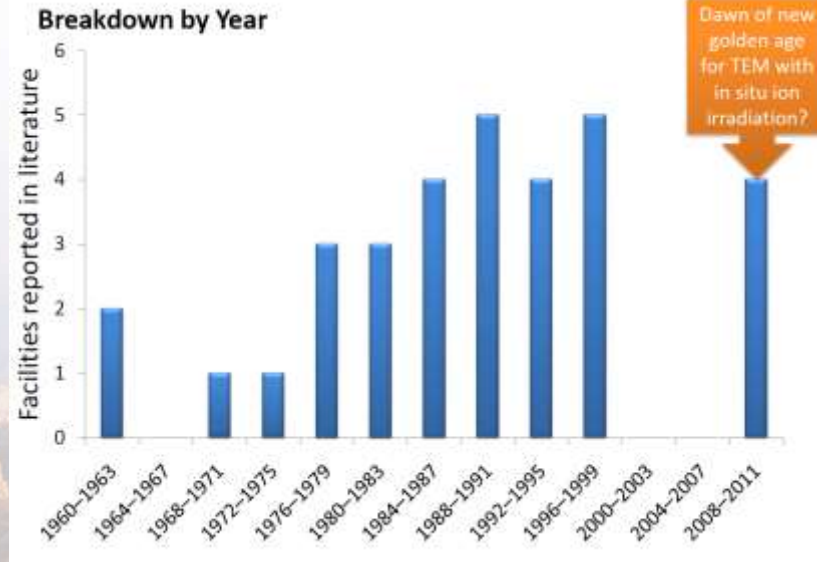
# History of *in situ* Irradiation TEM

Courtesy of: J. Hinks



*“The direct observation of ion damage in the electron microscope thus represents a powerful means of studying radiation damage”*

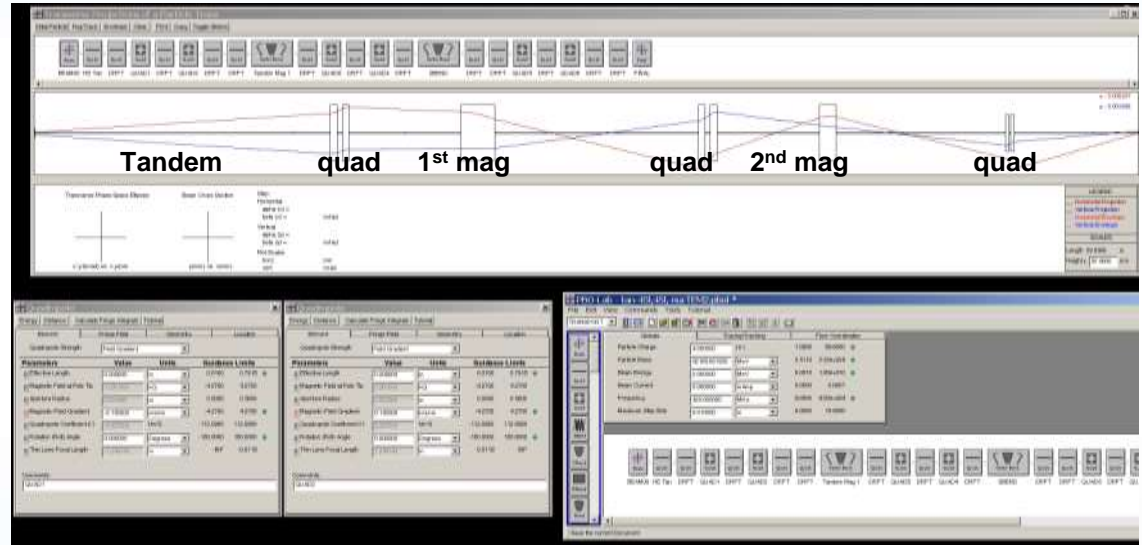
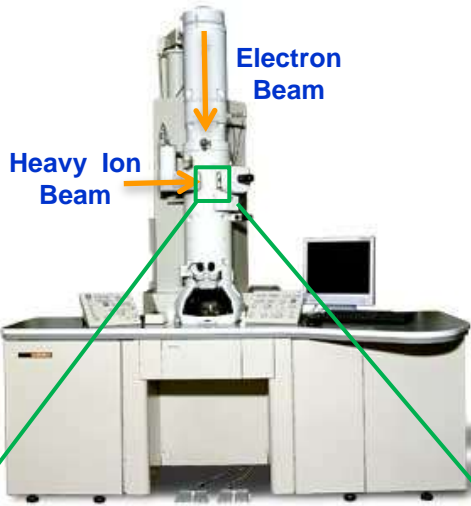
D.W. Pashley and A.E.B Presland *Philosophical Magazine* **6 (68)** (1961) p1002



# Beam Optic Models and Image Simulation of the *In situ* Ion Irradiation TEM

Collaborators: P. Rossi, D.L. Buller, & B.L. Doyle

## Ion Optics Feasibility Study

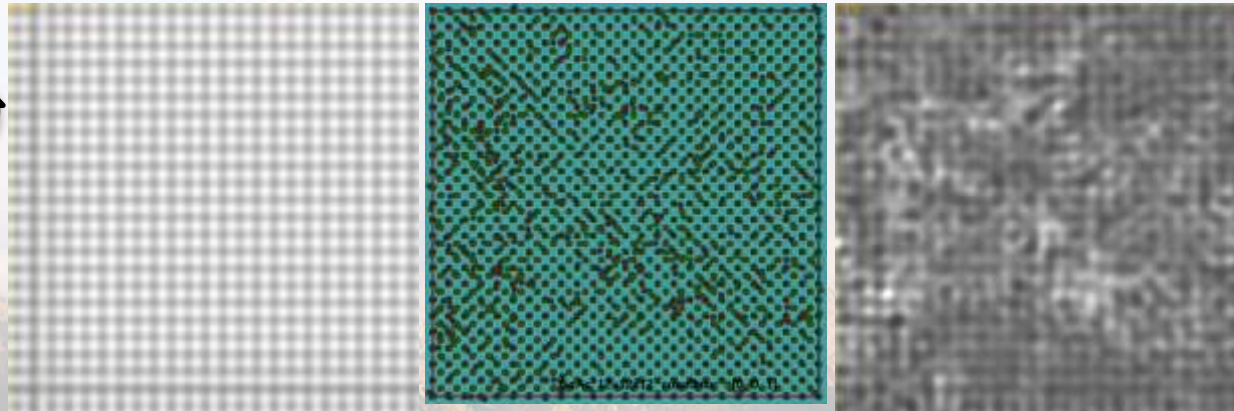
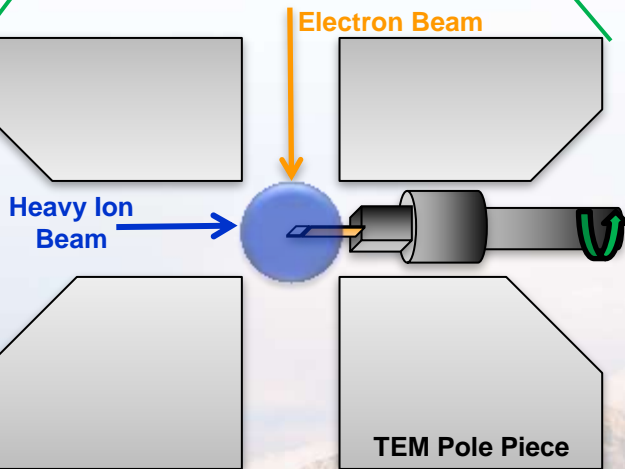


## TEM image simulation of radiation damage

JEMS undamaged

Marlowe

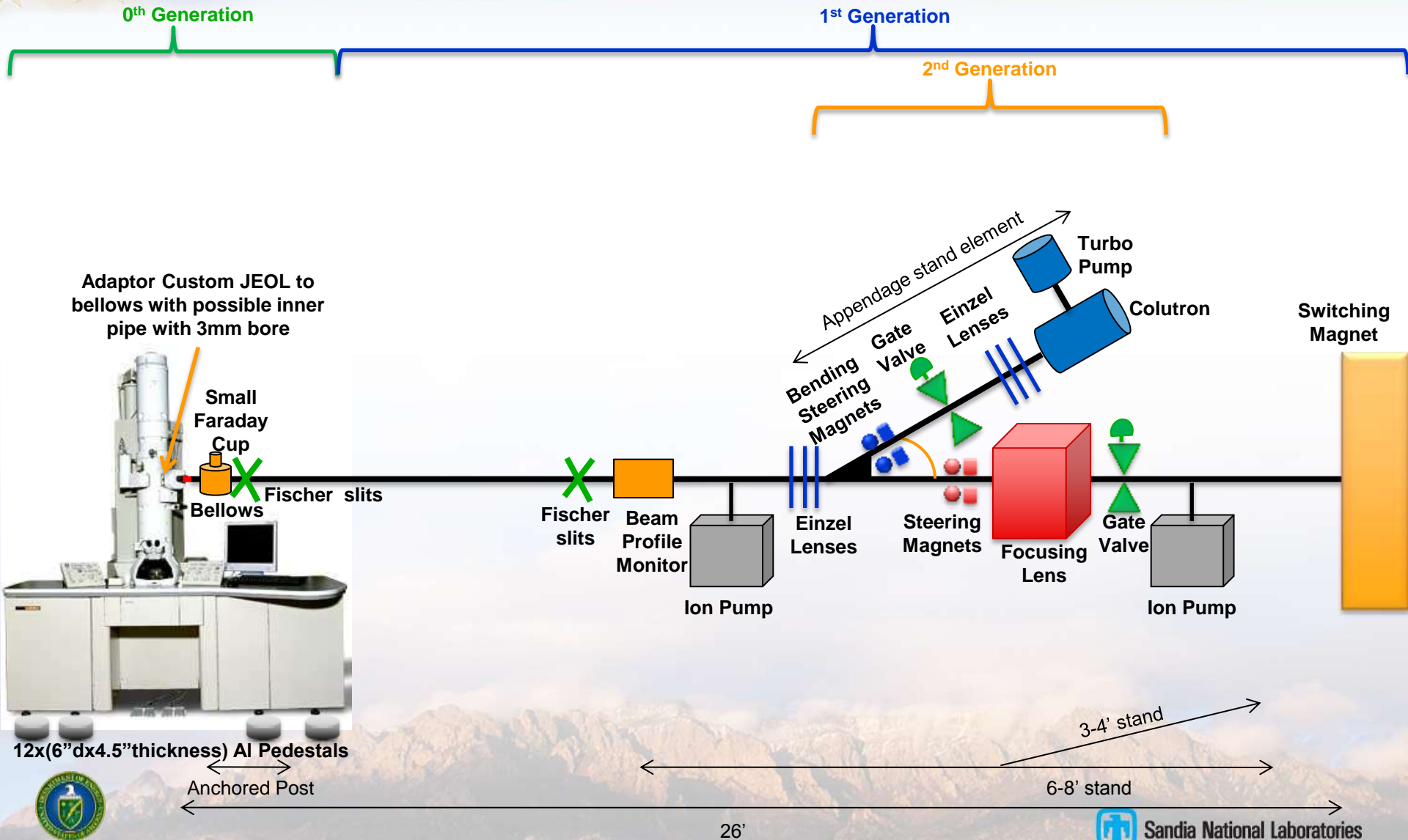
JEMS damaged



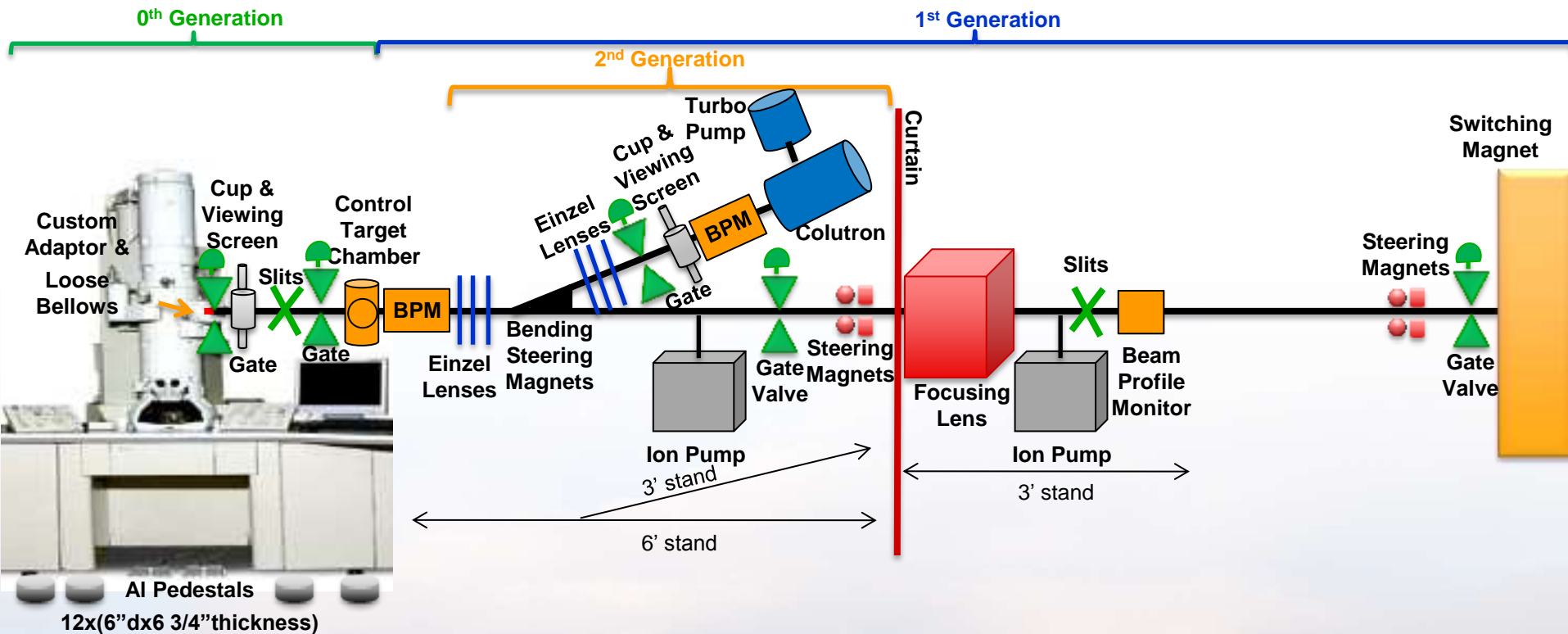
Simulation (Marlowe+JEMS) shows the project is viable (30 MeV Cu -> GaAs)



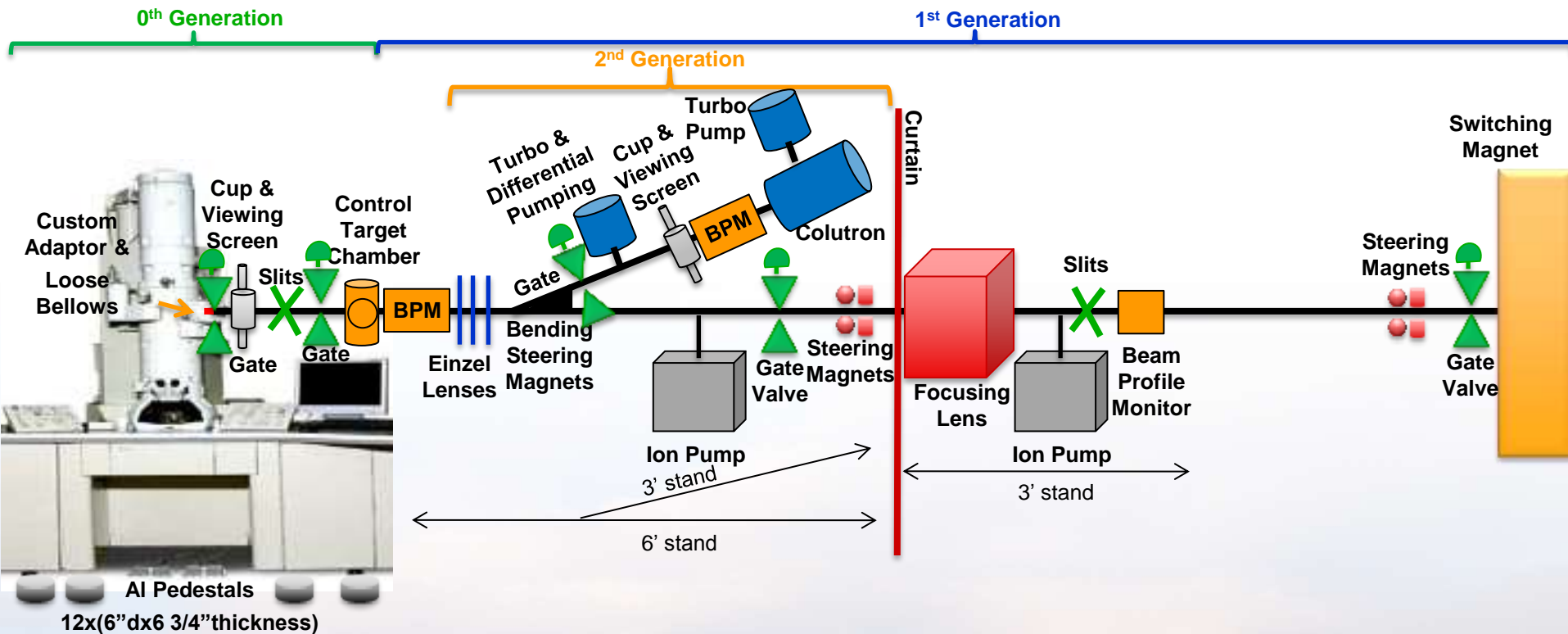
# Schematic of the *In situ* TEM Beamline



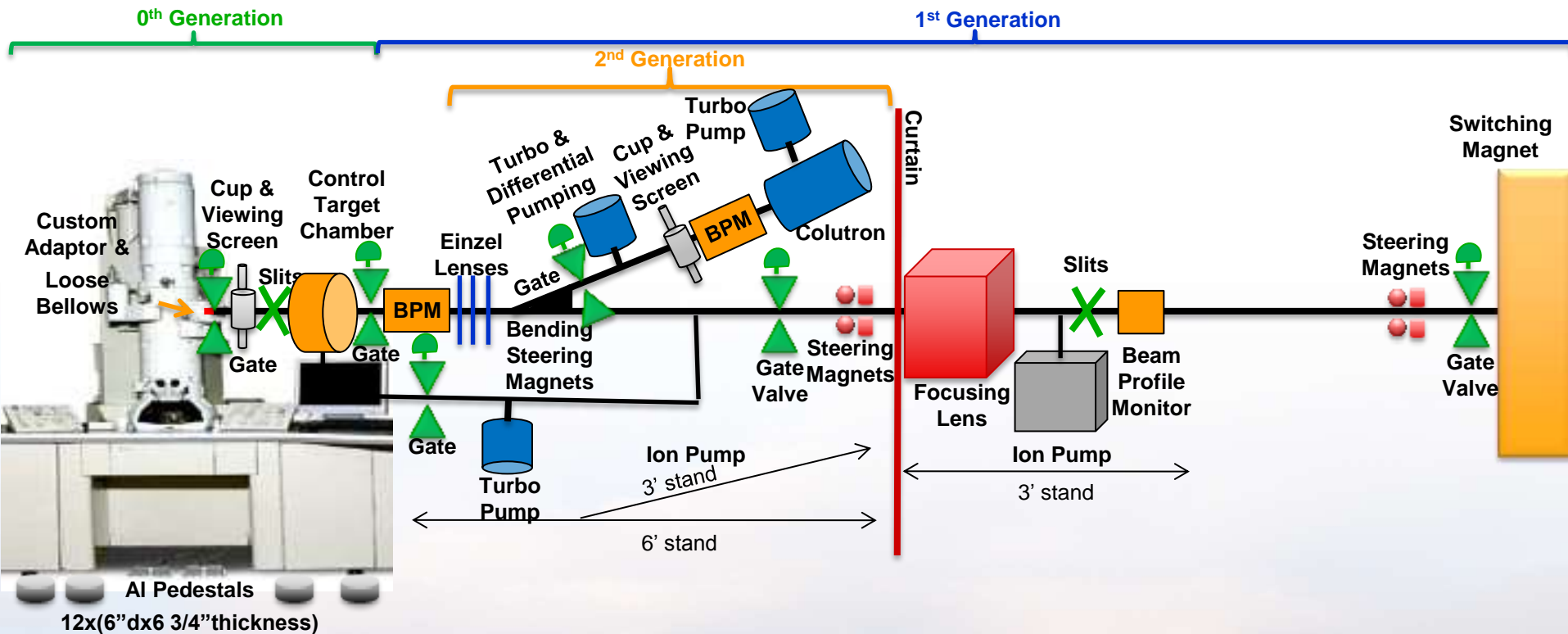
# Schematic of the *In situ* TEM Beamline



# Schematic of the *In situ* TEM Beamline



# Schematic of the *In situ* TEM Beamline



# Current Status of the *In situ* TEM Beamline

Collaborators: D.L. Buller & J.A. Scott



Beam burn from  
14 MeV Si

Gas Heating TEM  
Stage Controls

Microfluidic TEM  
Stage Controls

Double tilt stage  
needs to tilt only  
12°

10 kV  
Colutron

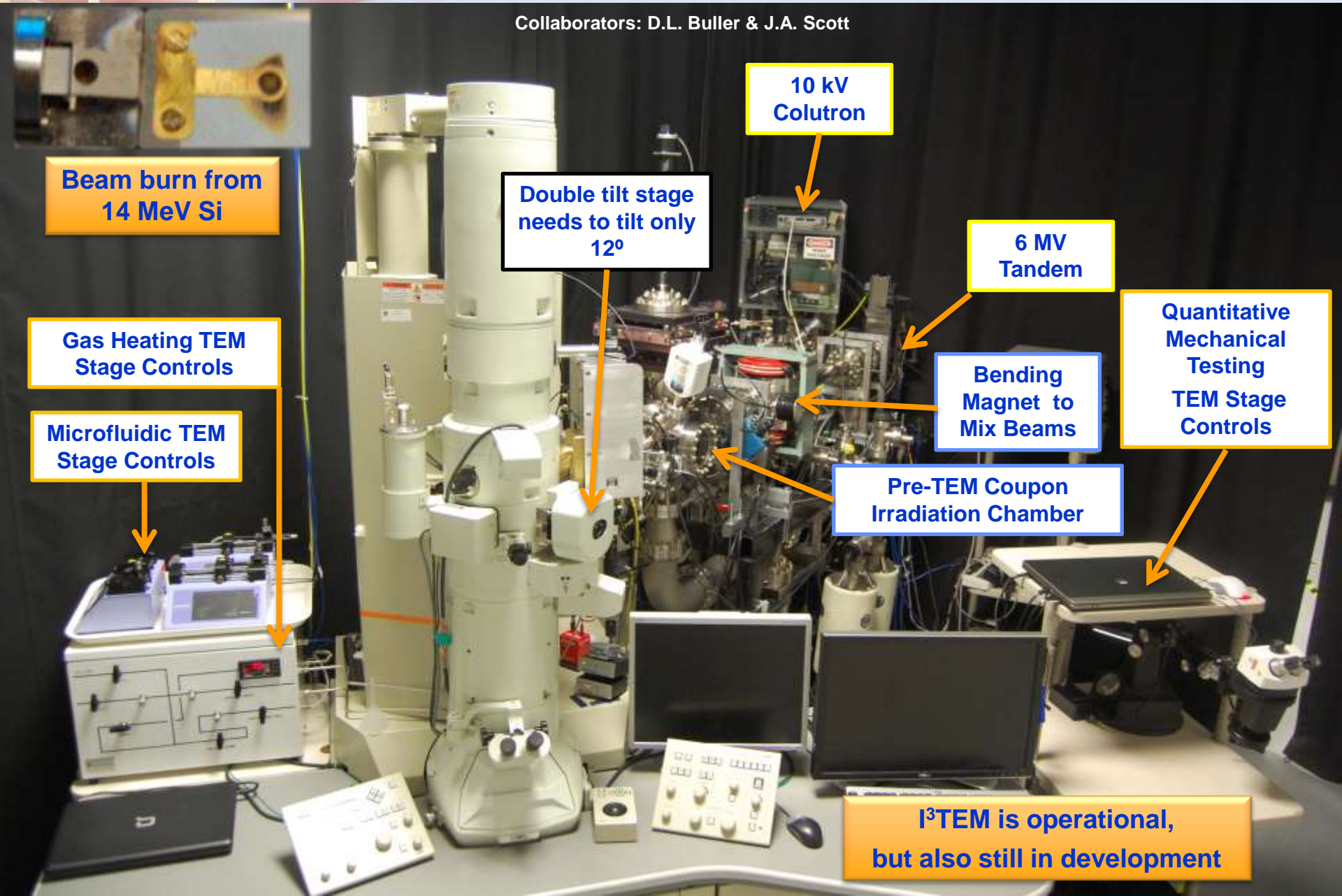
6 MV  
Tandem

Bending  
Magnet to  
Mix Beams

Quantitative  
Mechanical  
Testing  
TEM Stage  
Controls

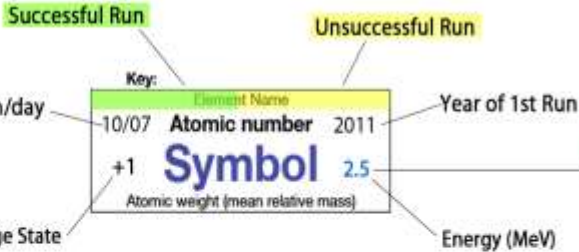
Pre-TEM Coupon  
Irradiation Chamber

I<sup>3</sup>TEM is operational,  
but also still in development



# Ion Species Attempted as of 7/23/2013

1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	
Hydrogen 10/7 1 2011 1+ <b>H</b> 1.008																	Helium 4/18 2 2011 1+ <b>He</b> 4.0026	
Lithium 3 <b>Li</b> 6.94	Beryllium 4 <b>Be</b> 9.0122											Boron 7/30 5 2013 2+ <b>B</b> 10.81	Carbon 7/08 6 2013 1+ <b>C</b> 12.011	Nitrogen 7 <b>N</b> 14.007	Oxygen 7/30 8 2013 2+ <b>O</b> 15.999	Fluorine 9 <b>F</b> 18.998	Neon 10 <b>Ne</b> 20.180	
Sodium 11 <b>Na</b> 22.990	Magnesium 12 <b>Mg</b> 24.305											Aluminum 7/18 13 2013 2+ <b>Al</b> 26.982	Silicon 4/14 14 2011 2+ <b>Si</b> 28.0855	Phosphorus 15 <b>P</b> 30.974	Sulfur 16 <b>S</b> 32.06	Chlorine 17 <b>Cl</b> 35.45	Argon 18 <b>Ar</b> 39.948	
Potassium 19 <b>K</b> 39.098	Calcium 20 <b>Ca</b> 40.078(4)		Scandium 21 <b>Sc</b> 44.956	Titanium 7/30 22 2013 3+ <b>Ti</b> 47.867	Vanadium 23 <b>V</b> 50.942	Chromium 7/26 24 2013 3+ <b>Cr</b> 51.996	Manganese 25 <b>Mn</b> 54.938	Iron 11/26 26 2012 2+ <b>Fe</b> 55.845(2)	Cobalt 27 <b>Co</b> 58.933	Nickel 11/4 28 2011 3+ <b>Ni</b> 58.693	Copper 9/15 29 2011 3+ <b>Cu</b> 63.546(3)	Zinc 30 <b>Zn</b> 65.38(2)	Gallium 7/30 31 2013 3+ <b>Ga</b> 69.723	Germanium 7/26 32 2013 3+ <b>Ge</b> 72.63	Arsenic 33 <b>As</b> 74.922	Selenium 34 <b>Se</b> 78.96(3)	Bromine 35 <b>Br</b> 79.904	Krypton 36 <b>Kr</b> 83.798(2)
Rubidium 37 <b>Rb</b> 85.468	Strontium 38 <b>Sr</b> 87.62		Yttrium 39 <b>Y</b> 88.906	Zirconium 40 <b>Zr</b> 91.224(2)	Niobium 41 <b>Nb</b> 92.906(2)	Molybdenum 42 <b>Mo</b> 95.96(2)	Technetium 43 <b>Tc</b> [97.91]	Ruthenium 44 <b>Ru</b> 101.07(2)	Rhodium 45 <b>Rh</b> 102.91	Palladium 46 <b>Pd</b> 106.42	Silver 7/02 47 2013 3+ <b>Ag</b> 107.87	Cadmium 48 <b>Cd</b> 112.41	Indium 49 <b>In</b> 114.82	Tin 7/26 50 2013 4+ <b>Sn</b> 118.71	Antimony 51 <b>Sb</b> 121.76	Tellurium 52 <b>Te</b> 127.60(3)	Iodine 53 <b>I</b> 126.90	Xenon 54 <b>Xe</b> 131.29
Caesium 55 <b>Cs</b> 132.91	Barium 56 <b>Ba</b> 137.33	57-70 *	Lutetium 71 <b>Lu</b> 174.97	Hafnium 72 <b>Hf</b> 178.49(2)	Tantalum 73 <b>Ta</b> 180.95	Tungsten 6/25 74 2012 4+ <b>W</b> 183.84	Rhenium 75 <b>Re</b> 186.21	Osmium 76 <b>Os</b> 190.23(2)	Iridium 77 <b>Ir</b> 192.22	Platinum 78 <b>Pt</b> 195.08	Gold 7/15 79 2011 3+ <b>Au</b> 196.97	Mercury 80 <b>Hg</b> 200.59	Thallium 81 <b>Tl</b> 204.38	Lead 82 <b>Pb</b> 207.2	Bismuth 83 <b>Bi</b> 208.98	Polonium 84 <b>Po</b> [209.96]	Astatine 85 <b>At</b> [209.99]	Radon 86 <b>Rn</b> [222.02]
Francium 87 <b>Fr</b> [223.02]	Radium 88 <b>Ra</b> [226.03]	89-102 **	Lanthanum 103 <b>Lr</b> [262.11]	Rutherfordium 104 <b>Rf</b> [265.12]	Dubnium 105 <b>Db</b> [268.13]	Seaborgium 106 <b>Sg</b> [271.13]	Bohrium 107 <b>Bh</b> [270]	Hassium 108 <b>Hs</b> [277.15]	Mtnerium 109 <b>Mt</b> [276.15]	Darmstadtium 110 <b>Ds</b> [281.16]	Roentgenium 111 <b>Rg</b> [280.16]	Copernicium 112 <b>Cn</b> [285.17]	Ununtrium 113 <b>Uut</b> [284.16]	Flerovium 114 <b>Fl</b> [289.10]	Ununpentium 115 <b>Uup</b> [288.10]	Livermorium 116 <b>Lv</b> [293]	Ununseptium 117 <b>Uus</b> [294]	Ununoctium 118 <b>Uuo</b> [294]



Current:  
HIGH (>100 nA)  
MEDIUM (1-100 nA)  
LOW (<1 nA)

\*lanthanoids

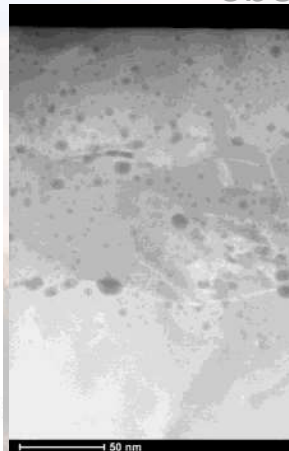
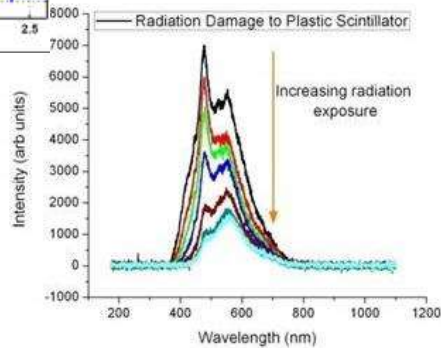
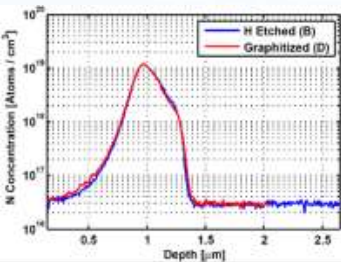
\*\*actinoids

Lanthanum 57 <b>La</b> 138.91	Cerium 58 <b>Ce</b> 140.12	Praseodymium 59 <b>Pr</b> 140.91	Neodymium 60 <b>Nd</b> 144.24	Promethium 61 <b>Pm</b> [144.91]	Samarium 62 <b>Sm</b> 150.36(2)	Europium 63 <b>Eu</b> 151.96	Gadolinium 64 <b>Gd</b> 157.25(3)	Terbium 65 <b>Tb</b> 158.93	Dysprosium 66 <b>Dy</b> 162.50	Holmium 67 <b>Ho</b> 164.93	Erbium 68 <b>Er</b> 167.26	Thulium 69 <b>Tm</b> 168.93	Ytterbium 70 <b>Yb</b> 173.05
Actinium 89 <b>Ac</b> [227.03]	Thorium 90 <b>Th</b> 232.04	Protactinium 91 <b>Pa</b> 231.04	Uranium 92 <b>U</b> 238.03	Neptunium 93 <b>Np</b> [237.05]	Plutonium 94 <b>Pu</b> [244.06]	Americium 95 <b>Am</b> [243.06]	Curium 96 <b>Cm</b> [247.07]	Berkelium 97 <b>Bk</b> [247.07]	Californium 98 <b>Cf</b> [251.08]	Einsteinium 99 <b>Es</b> [252.08]	Fermium 100 <b>Fm</b> [257.10]	Mendelevium 101 <b>Md</b> [258.10]	Nobelium 102 <b>No</b> [259.10]

# Outline

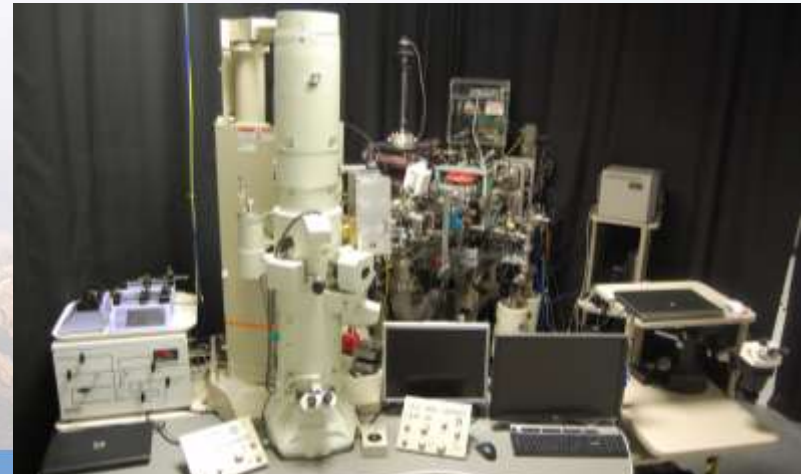
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- Control of Local Chemistry
  - ♦ Development of back gates for graphene devices
- Investigate Radiation Tolerance
  - ♦ Various radiation detectors from MOFs to complex oxides
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  - ♦ Improving the wear properties of electrical contacts



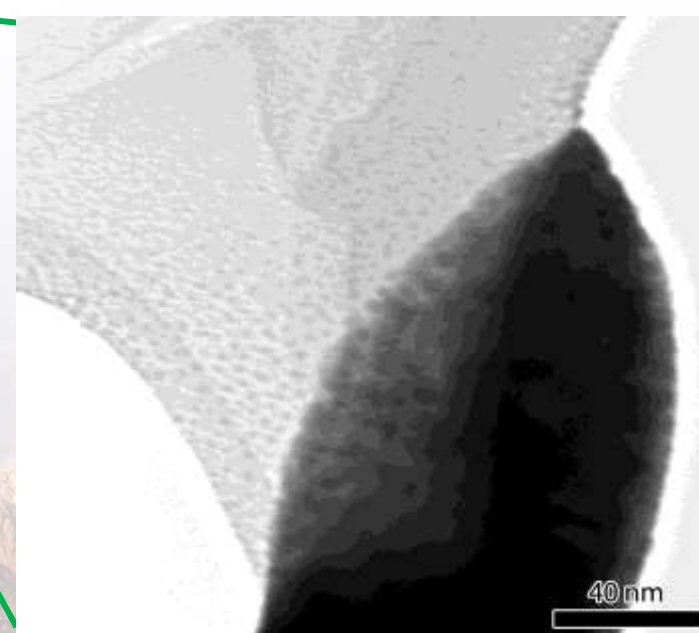
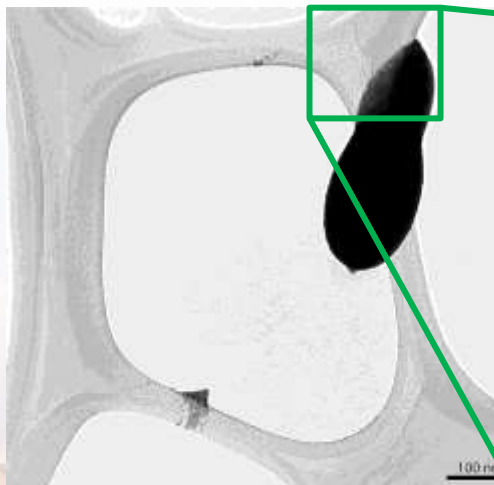
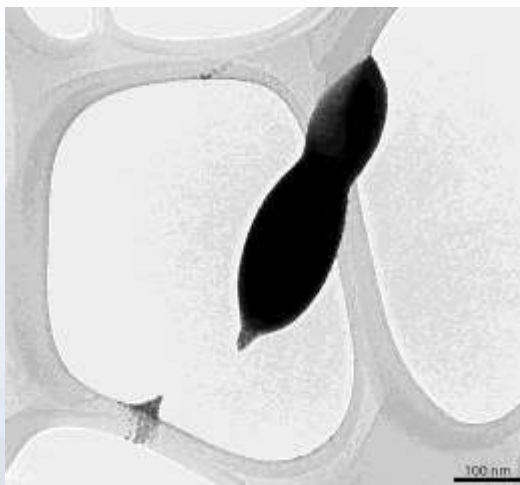
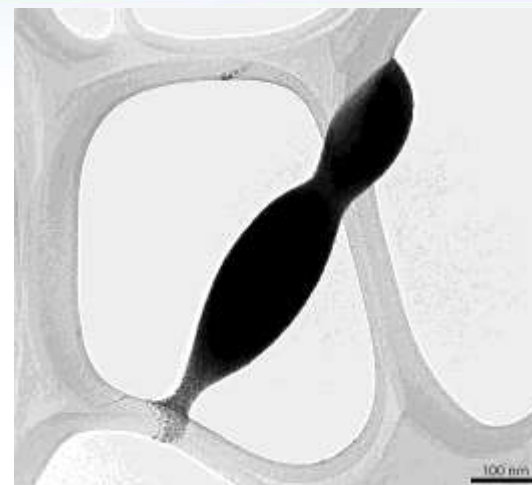
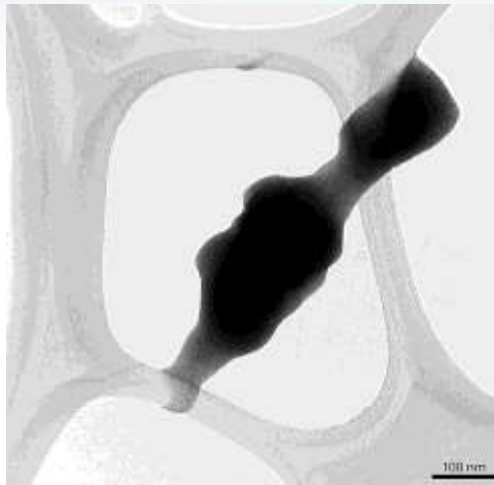
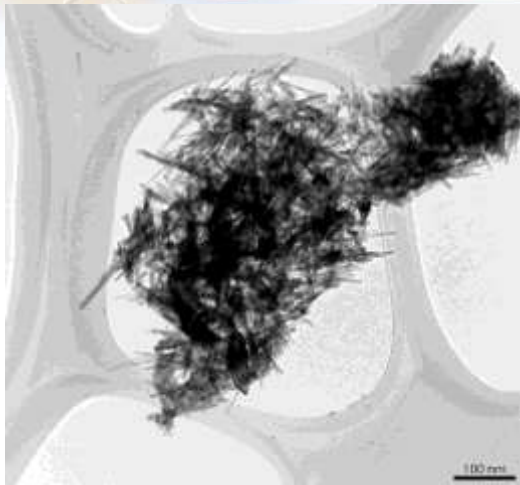
## 2. Materials Science

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- Fun future directions for real-time nanoscale observation in extreme environments



# CdWO<sub>4</sub> Irradiated with 50 nA of 3 MeV Cu<sup>3+</sup>

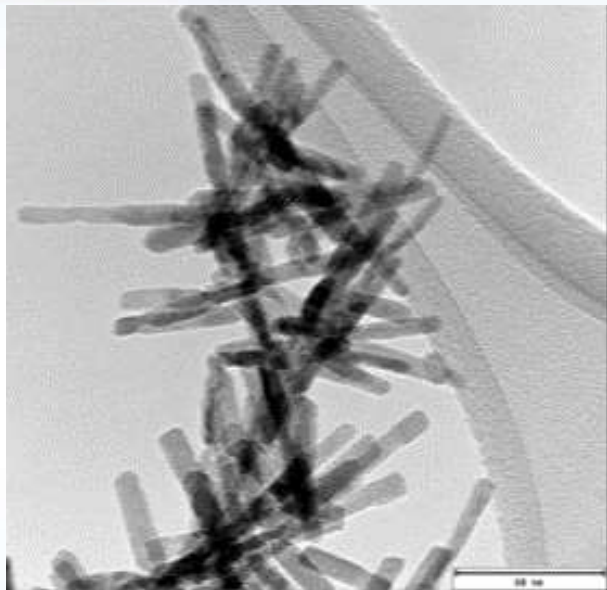
Collaborators: S.M. Hoppe & B.A. Hernandez-Sanchez



Over 1 hr, nanorods broke into small pieces and sputtered onto nearby lace.

# Radiation Tolerance is Needed in Advanced Scintillators for Non-proliferation Applications

Contributors: S.M. Hoppe, B.A. Hernandez-Sanchez, T. Boyle



High-Z nanoparticles are promising, but are radiation sensitive

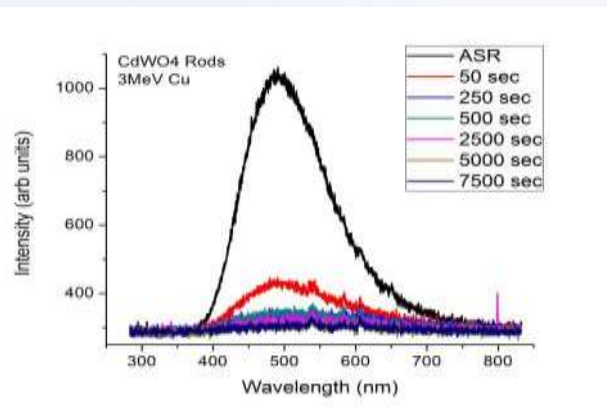
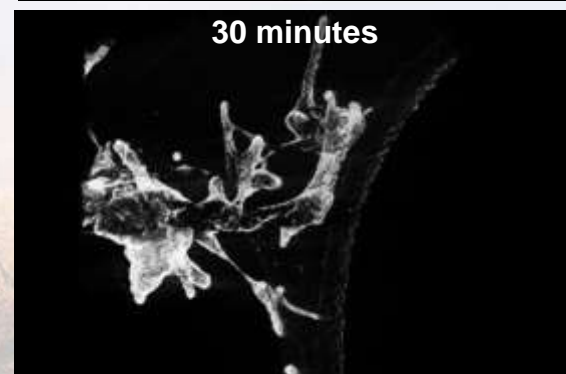
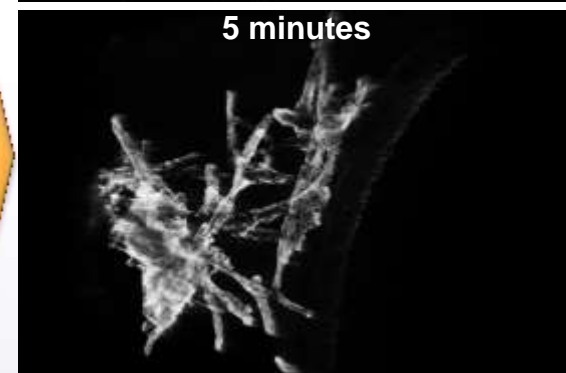
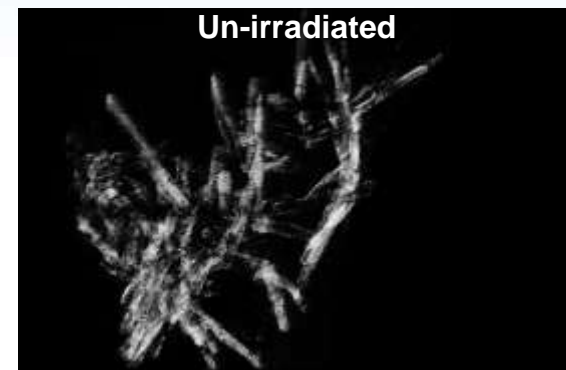
## *In situ* Ion Irradiation TEM (I<sup>3</sup>TEM)



Hummingbird tomography stage

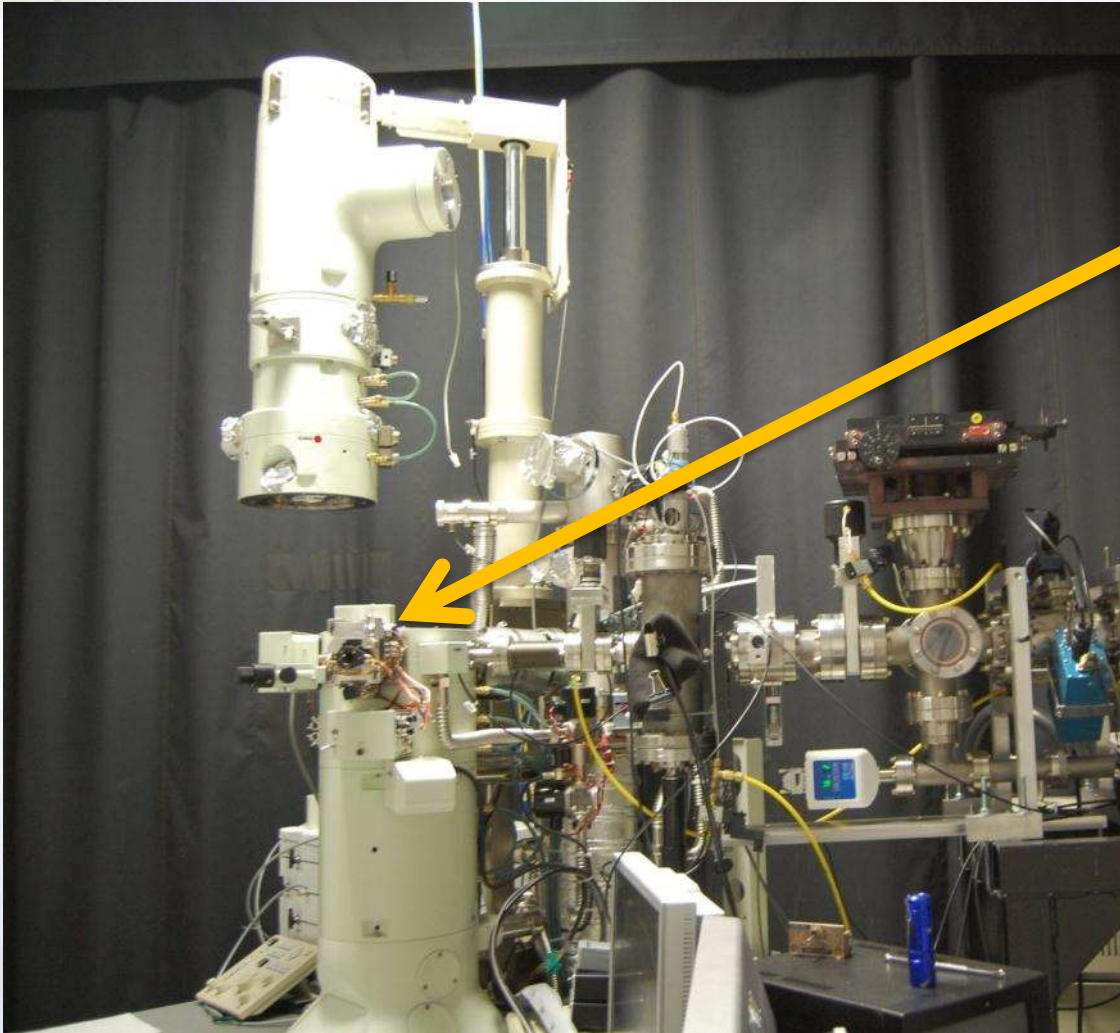


Tomography of Irradiated CdWO<sub>4</sub>:  
3 MeV Cu<sup>3+</sup> at ~30 nA



# Current work: *In situ* TEM Luminescence

Collaborators: D. Masiel



Optical Mirror in TEM



First IBIL in TEM



## Optical Pathway in an I<sup>3</sup>TEM

- Angled mirror with bore hole for the electron path was installed.
- Mirror is located on top of the objective polepiece “heart of the TEM”
- Port is being constructed with thick leaded glass to permit light through, but not x-rays created by ion or electron beams.
- Should permit *in situ* IBIL and CL.

An optical port is currently being added to the I<sup>3</sup>TEM, which, if successful, will permit *in situ* TEM luminescence studies (CL and IBIL)

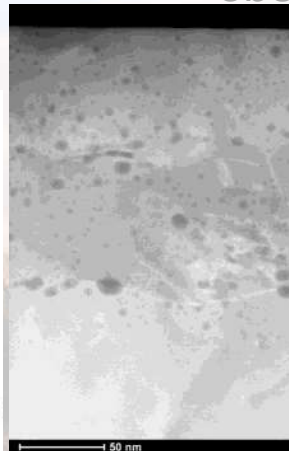
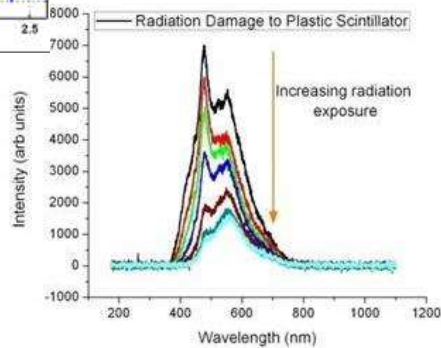
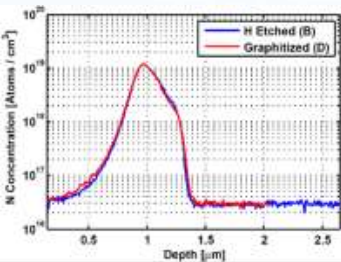


Sandia National Laboratories

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## 2. Materials Science

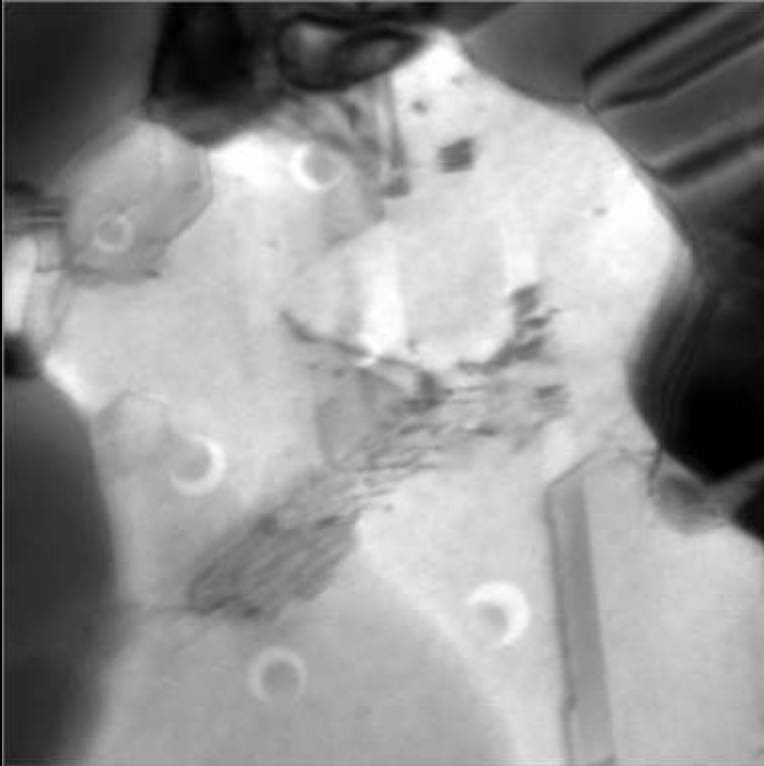
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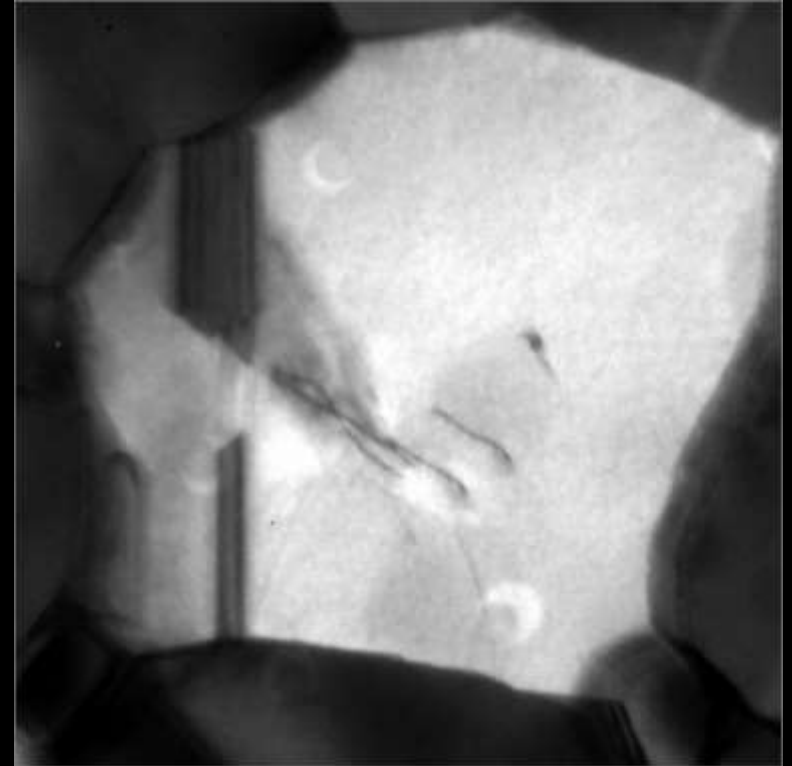
# Single Ion Strikes

Collaborators: C. Chisholm & A. Minor

$7.9 \times 10^9$  ions/cm<sup>2</sup>/s



$6.7 \times 10^7$  ions/cm<sup>2</sup>/s

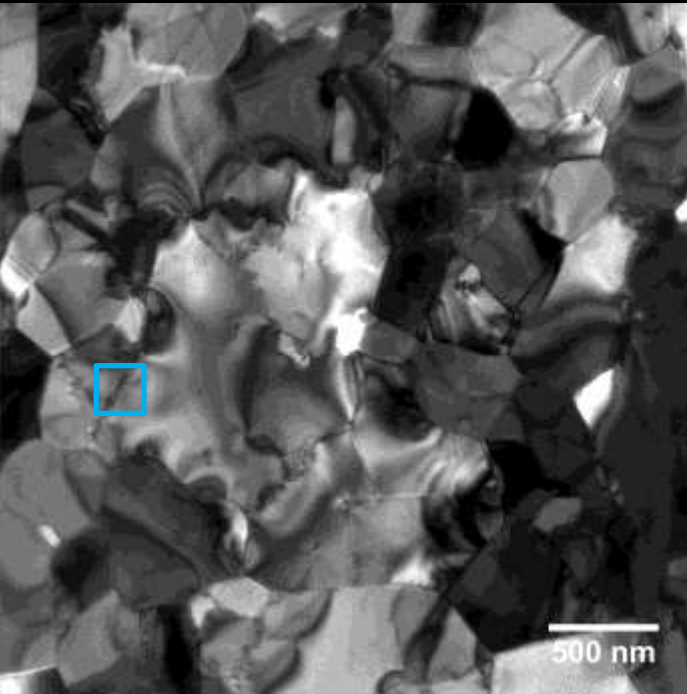


**VS**

Improved vibrational and ion beam stability permits us to work at 120kx or higher permitting imaging of single cascade events

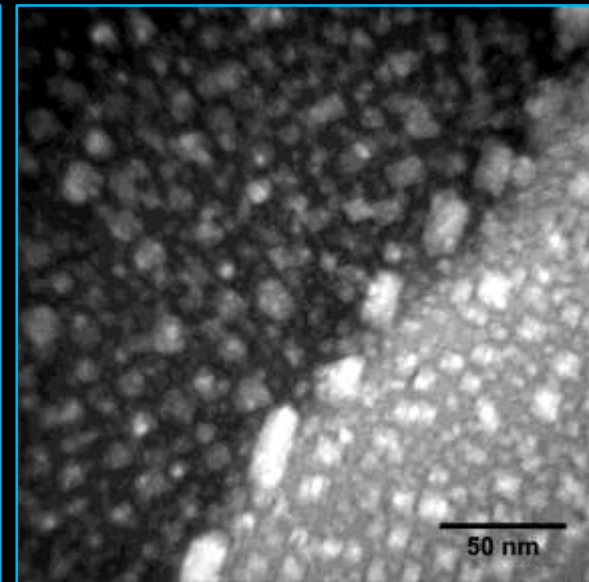
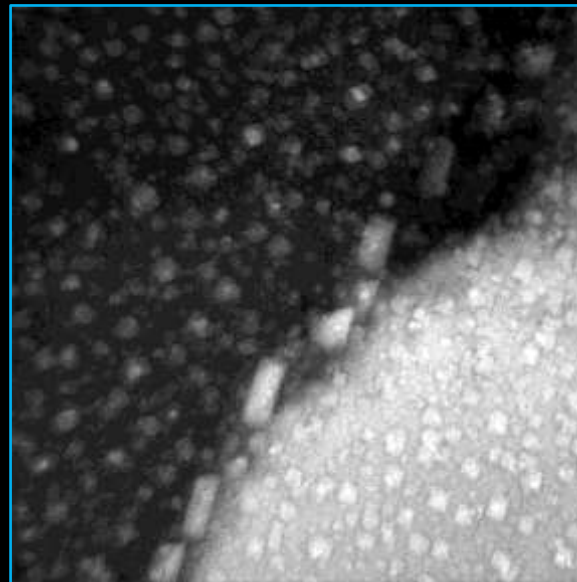
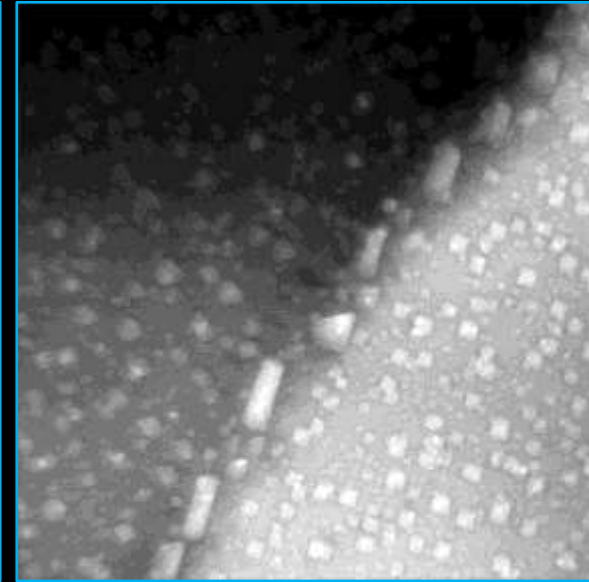
# *In situ* Implantation

Collaborators: C. Chisholm & A. Minor



**Gold thin-film implanted  
with 10keV He<sup>2+</sup>**

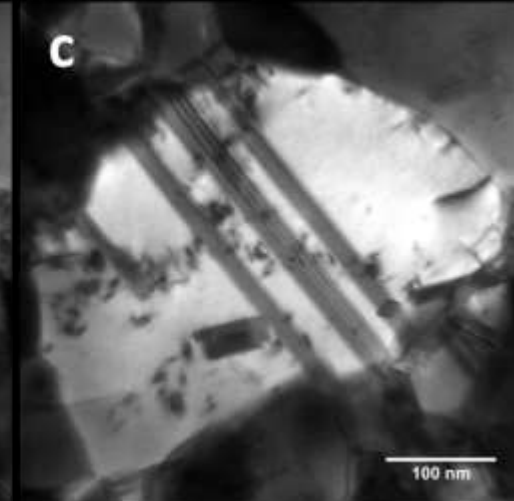
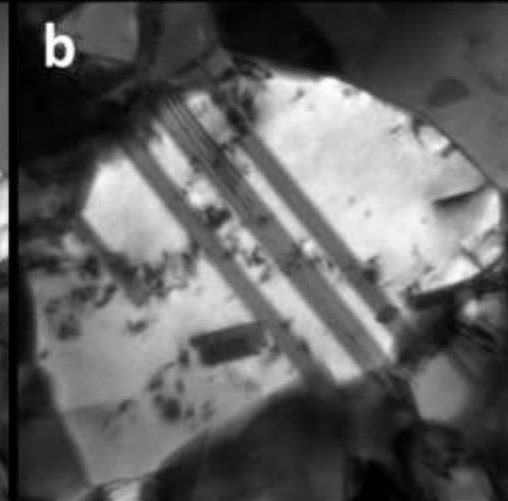
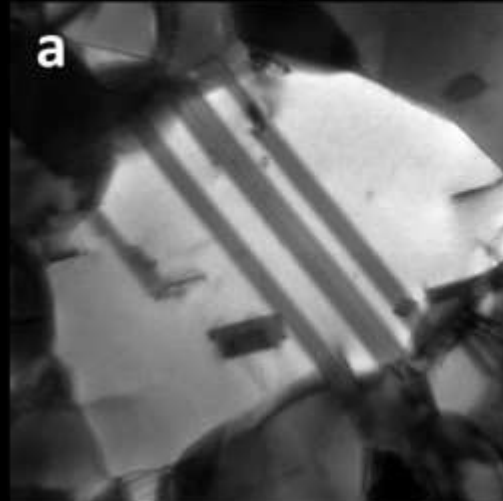
**Result: porous  
microstructure**



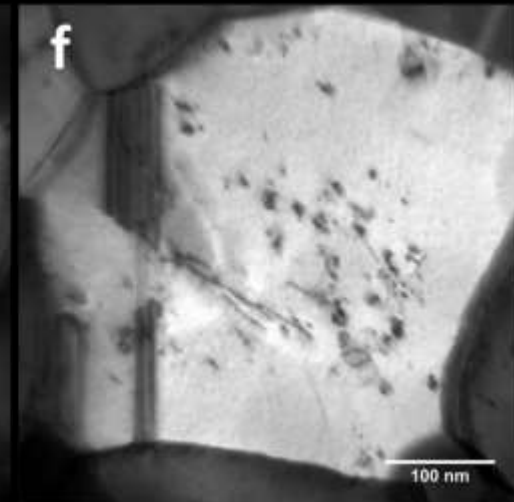
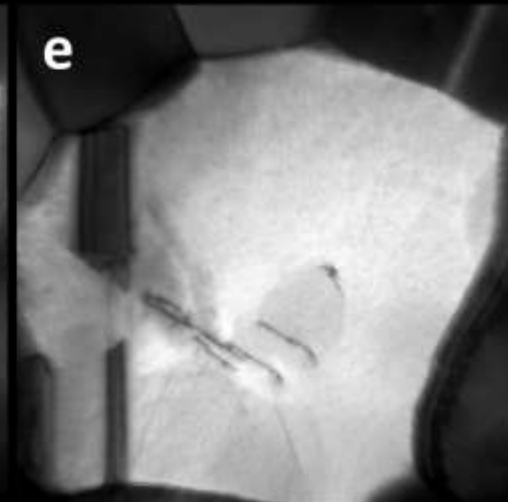
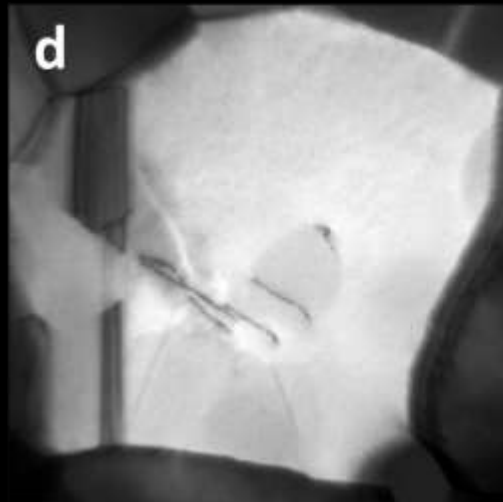
# *in situ* Successive Implantation & Irradiation

Collaborators: C. Chisholm & A. Minor

Successive  $\text{Au}^{4+}$  then  $\text{He}^{1+}$



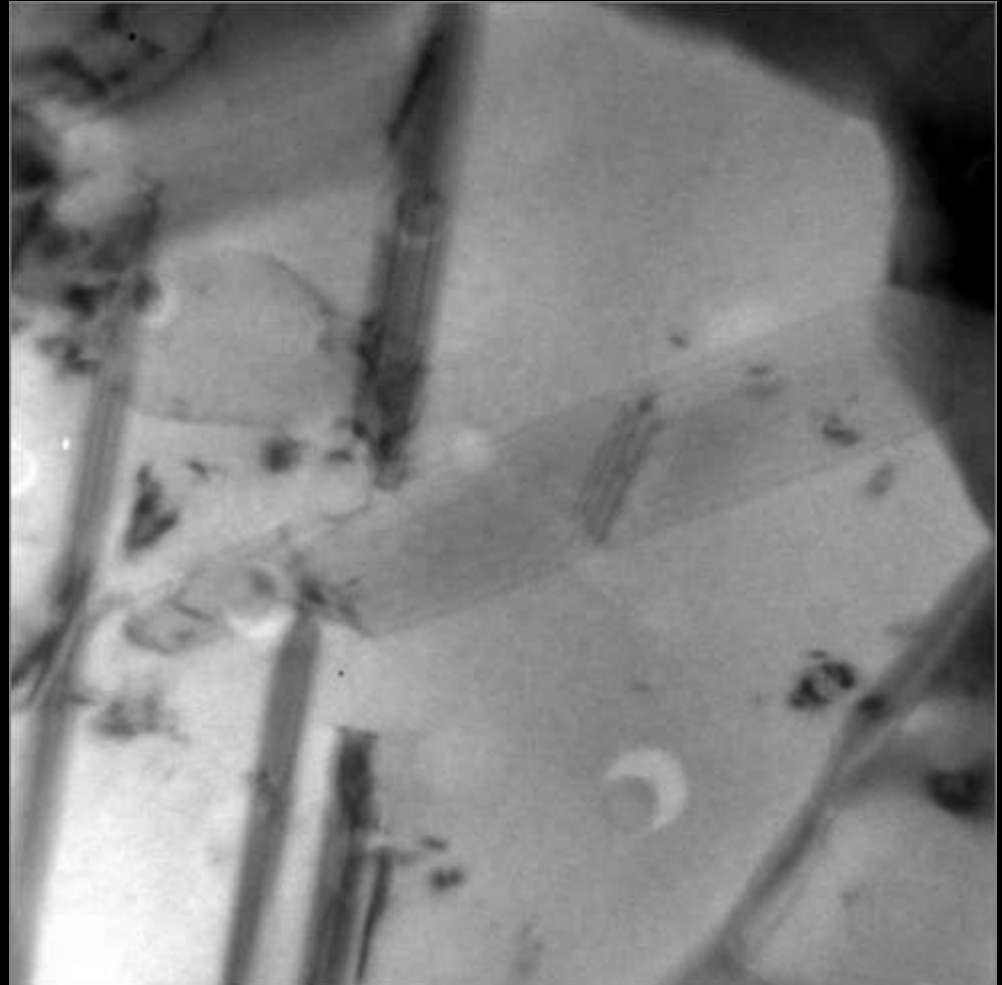
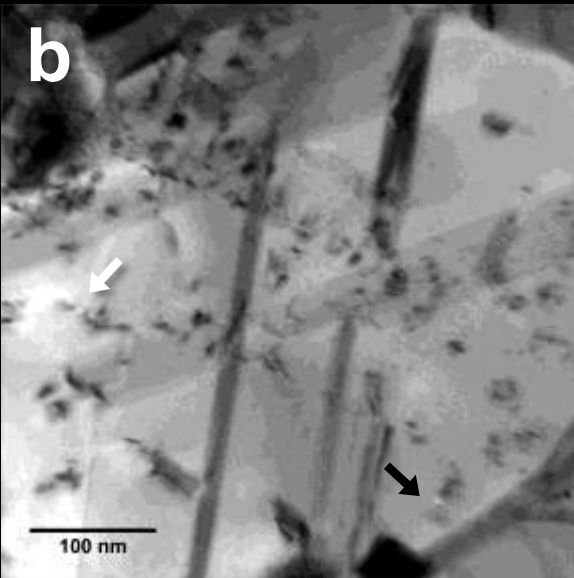
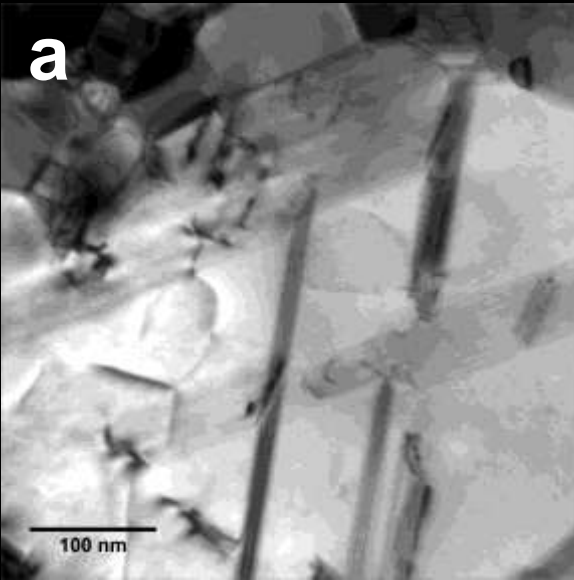
Successive  $\text{He}^{1+}$  then  $\text{Au}^{4+}$



# *In situ* Concurrent Implantation & Irradiation

Collaborators: C. Chisholm & A. Minor

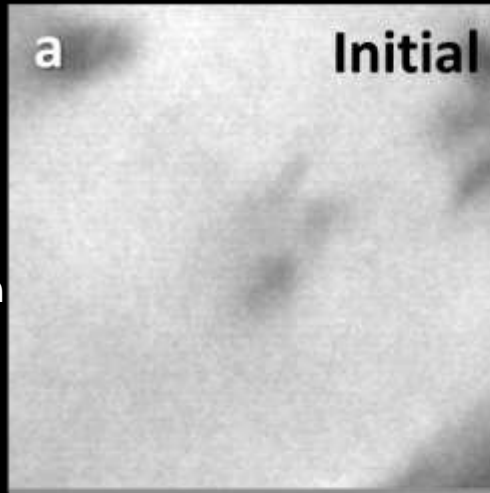
$\text{He}^{1+}$  implantation and  $\text{Au}^{4+}$  irradiation  
of a gold thin film



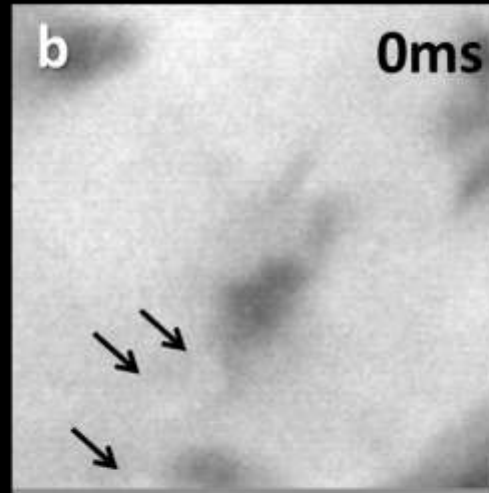
# Single Ion Strikes During Concurrent Irradiation: Nucleation of Helium Cavities

Collaborators: C. Chisholm & A. Minor

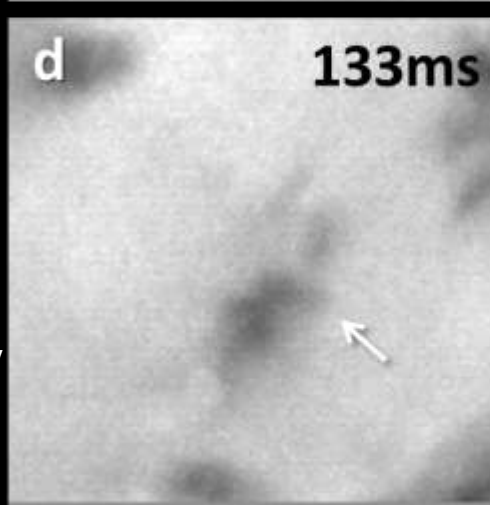
a) Initial microstructure



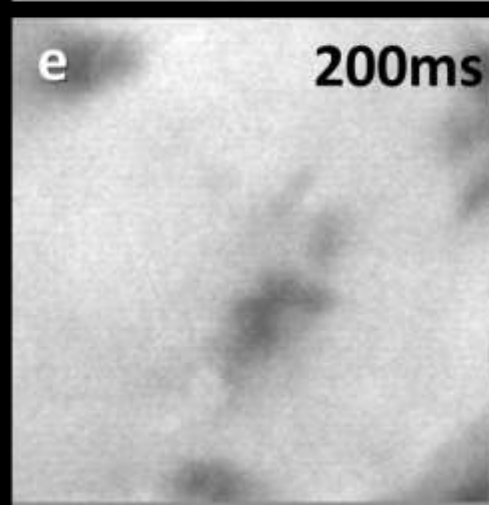
b) Cascade: Creation of dislocation loops, vacancy clusters, and three cavities



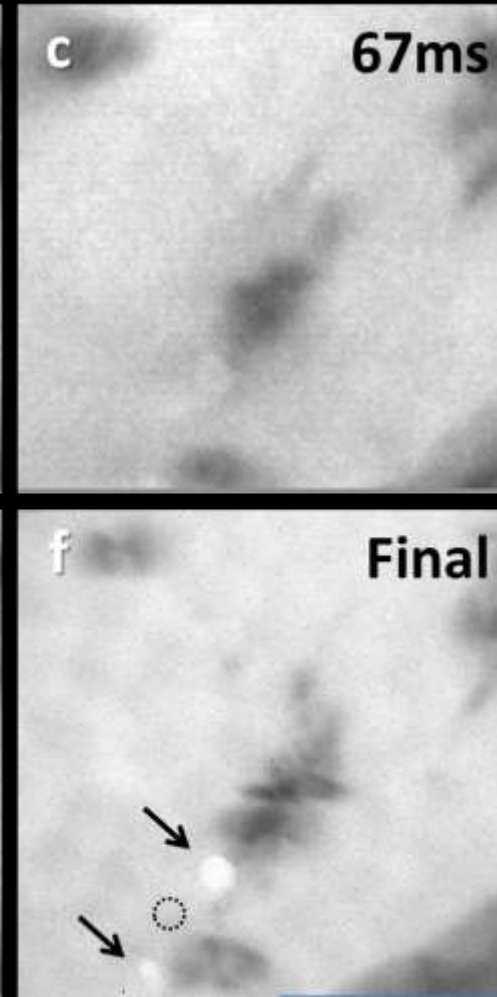
d) Cascade damage still evolving



e) Apparent stability



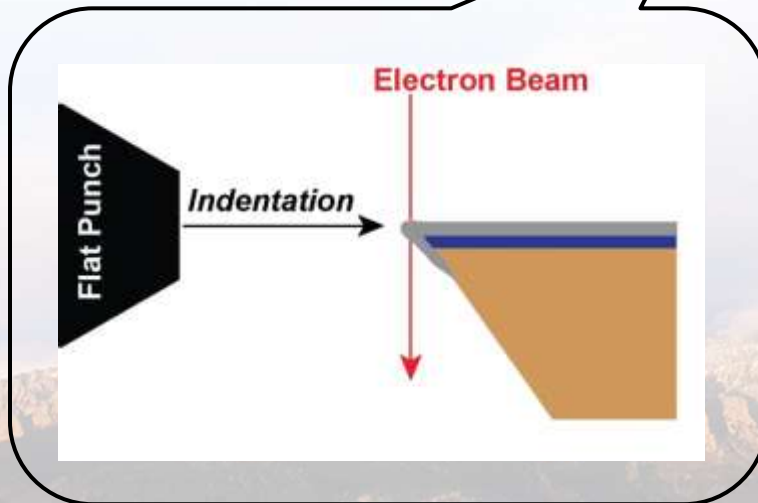
f) Final microstructure: Only two remaining cavities



# Specimen Synthesis & Testing

## In situ TEM Fatigue

- Microscope: JEOL JEM 2100 LaB<sub>6</sub> TEM
- Holder: Hysitron PI-95 PicoIndenter with a 1 $\mu$ m flat tip punch



## Sample Fabrication



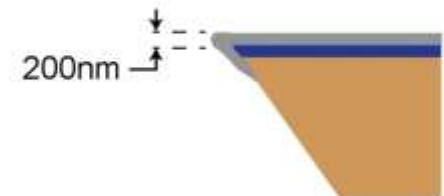
1. Start with Si wafer coated with nitride



2. Open window in nitride



3. Anisotropic wet etch (TMAH) exposes 111 plane to create a wedge



4. Pulse laser deposition of Al onto wedge



# *In situ* TEM Quantitative Mechanical Testing

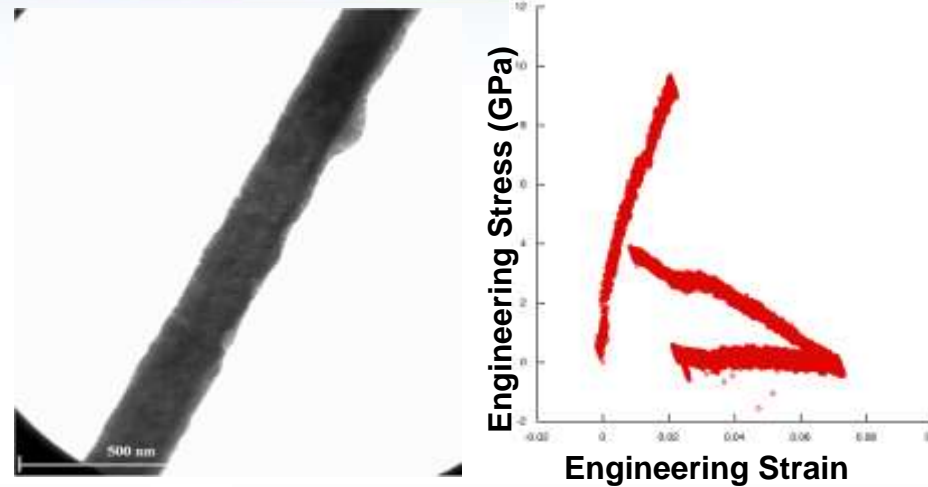
Contributors: J. Sharon, B. L. Boyce, C. Chisholm, H. Bei, E.P. George, P. Hosemann, A.M. Minor, & Hysitron Inc.

## Radiation effect on mechanical properties

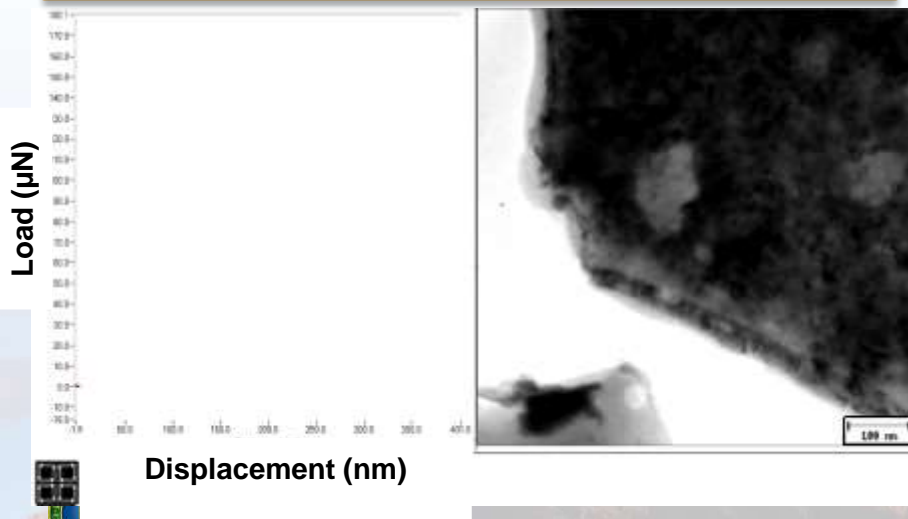
- Direct correlation of dose and defect density with resulting change in strength and ductility
- Failure of Mo-wire after 3 MeV Cu irradiation

## Contact and fatigue effect on structure

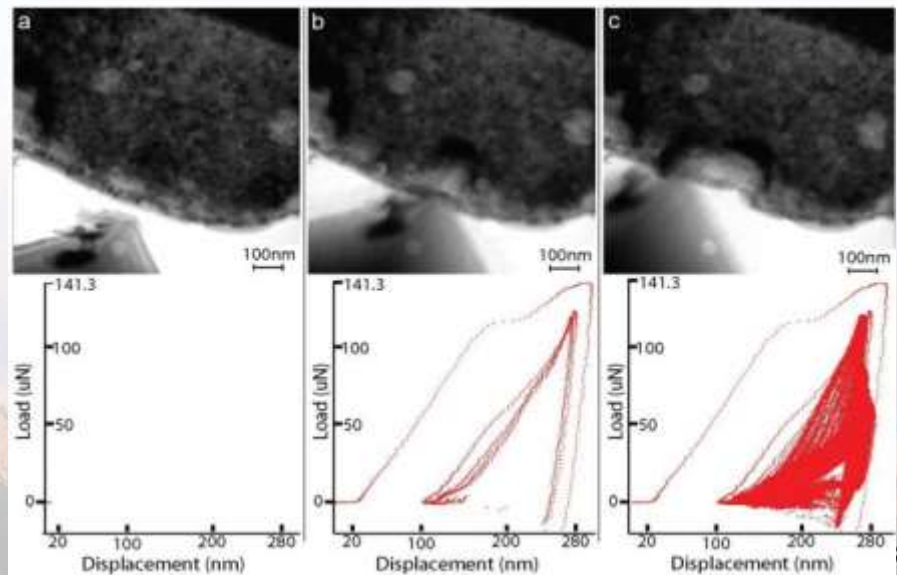
- Associate change in local hardness and fatigue with corresponding nanostructure
- Indent and Fatigue of nanocrystalline Cu film



## Fundamentals of contact reliability

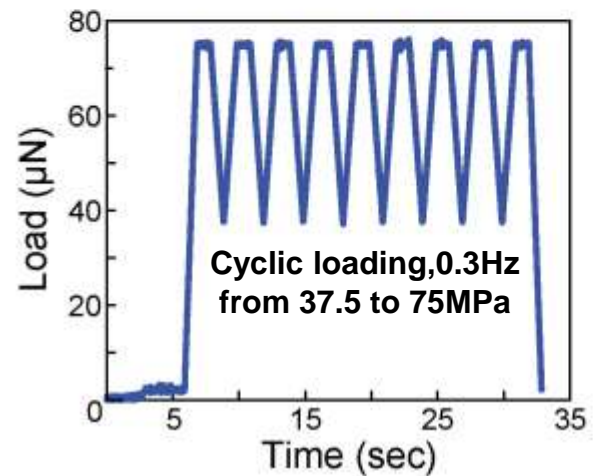
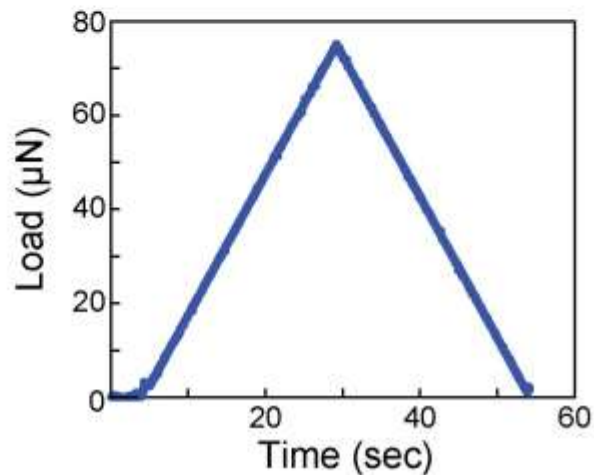
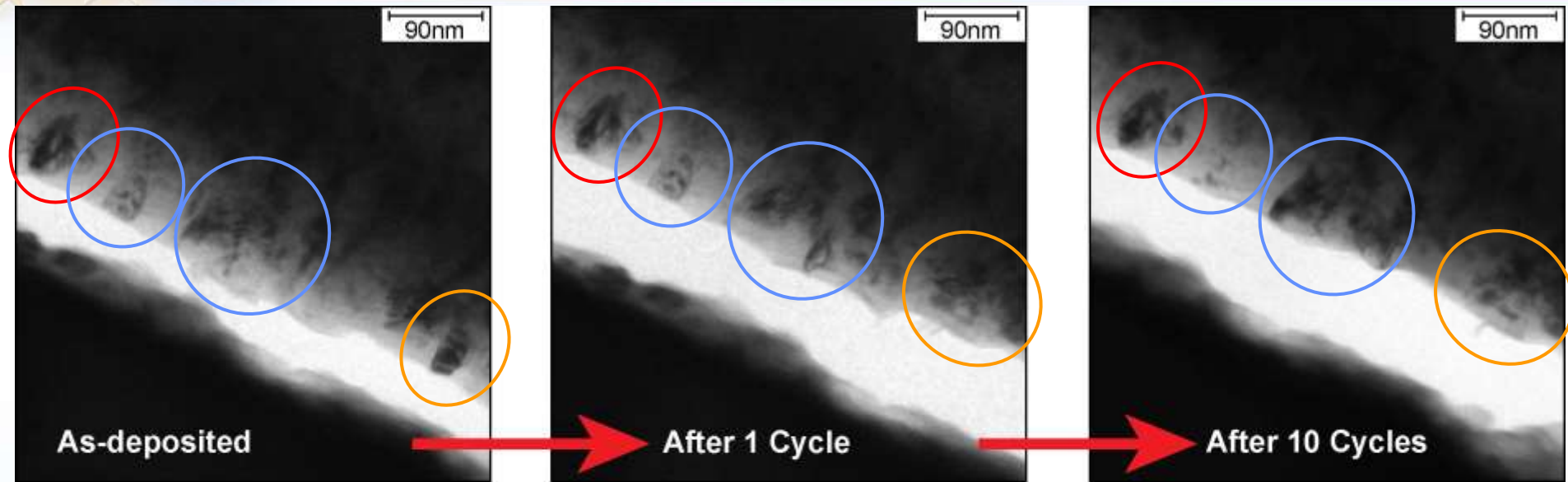


## Displacement damage effect on mech. prop.



# No, Monotonic, or Cyclic Evolution

Contributors: J. Sharon, B. L. Boyce

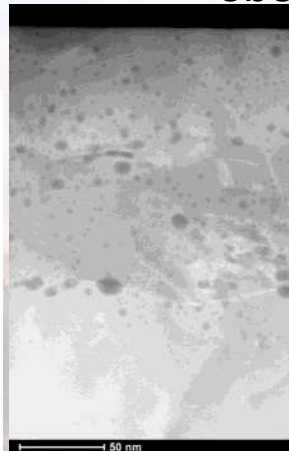
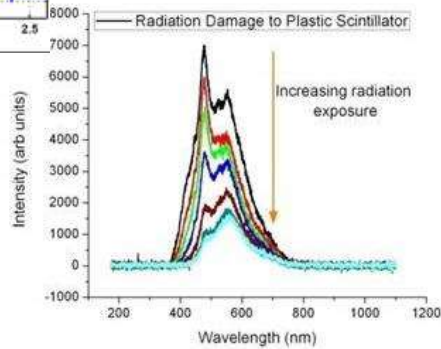
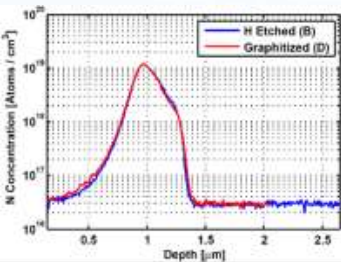


375 MPa nominal contact stress

# Outline

## 1. Materials Engineering

- Control of Local Chemistry
  - ♦ Development of back gates for graphene devices
- Investigate Radiation Tolerance
  - ♦ Various radiation detectors from MOFs to complex oxides
- Control of Local Structure
  - ♦ Improving the wear properties of electrical contacts



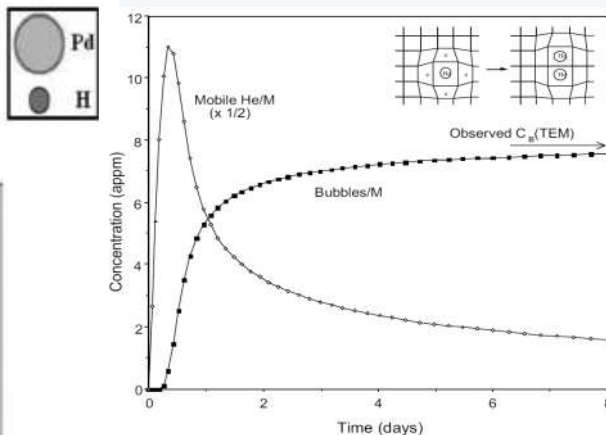
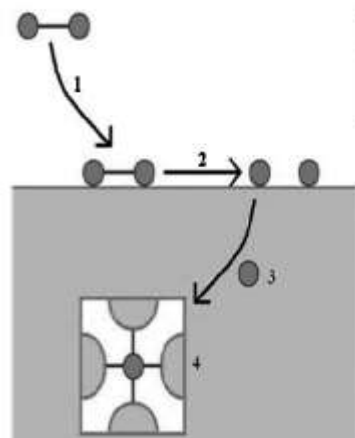
## 2. Materials Science

- Broad Capability of the I<sup>3</sup>TEM
- Revisit of the Radiation Detectors
  - ♦ In-situ ion irradiation of high-z nanoscintillators
- Revisit of the Structural Control
  - ♦ In-situ study of Au electrode evolution under ion beam modification
  - ♦ Initial work on indentation and cyclic compression
- Fun future directions for real-time nanoscale observation in extreme environments



# Can *In situ* TEM Address Hydrogen Storage Concerns in Extreme Environments?

Contributors: B.G. Clark, P.J. Cappillino, B.W. Jacobs, M.A. Hekmaty, D.B. Robinson, L.R. Parent, I. Arslan. & Protochips, Inc.



R. Delmelle, J., Phys. Chem. Chem. Phys. (2011) p.11412

Cowgill, D., Fusion Sci. & Tech., 28 (2005) p. 539

Trinkaush, H. et al., JNM (2003) p. 229

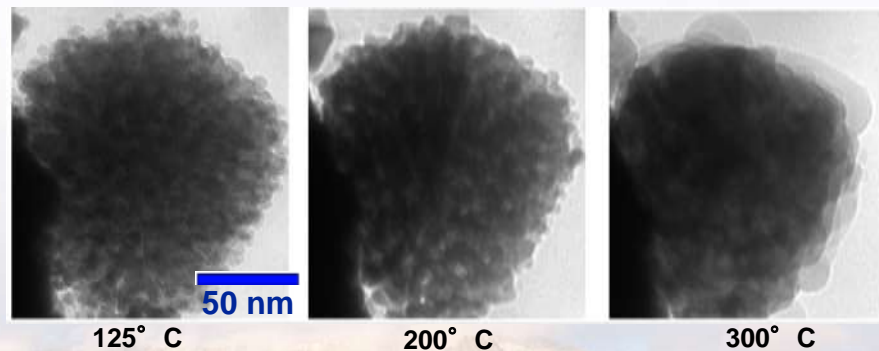
Thiebaud, S. et al. JNM (2000) p. 217

## Vapor-Phase Heating TEM Stage

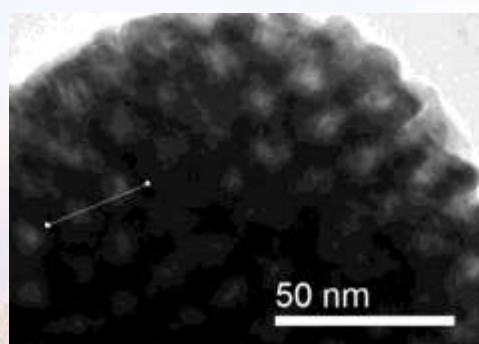
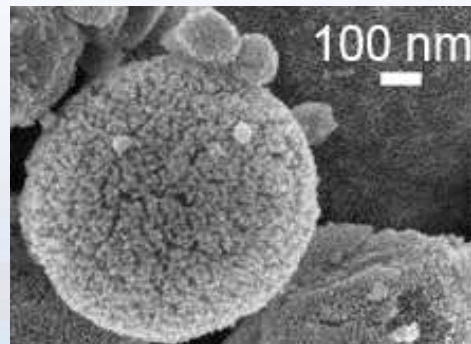
- Compatible with a range of gases
- In situ* resistive heating
- Continuous observation of the reaction channel
- Chamber dimensions are controllable
- Compatible with MS and other analytical tools



- 1 atm H<sub>2</sub> after several pulses to specified temp.



Harmful effects may be mitigated in nanoporous Pd



New *in situ* atmospheric heating experiments provide great insight into nanoporous Pd stability

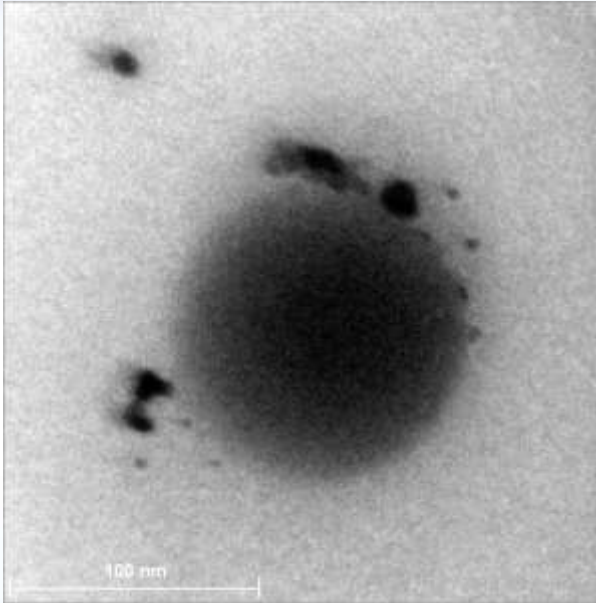


# Other Fun Uses of Microfluidic Cell

## Protocell Drug Delivery

S. Hoppe,  
E. Carnes,  
J. Brinker

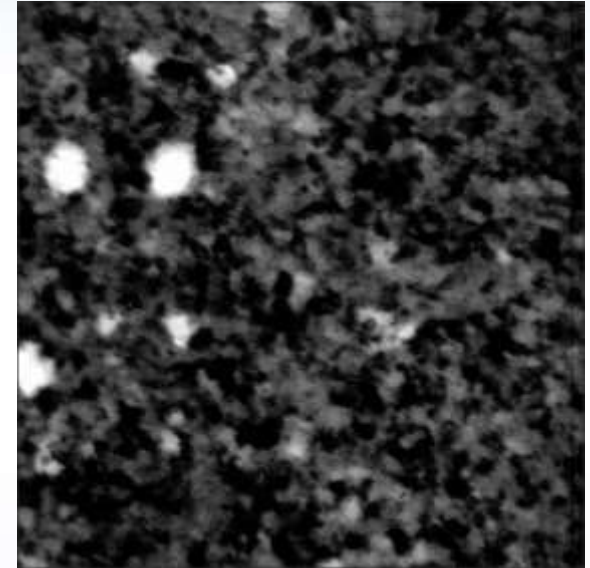
Liposome  
encapsulated  
Silica destroyed  
by the electron  
beam



## Metal Corrosion

D. Gross, J. Kacher,  
I.M. Robertson

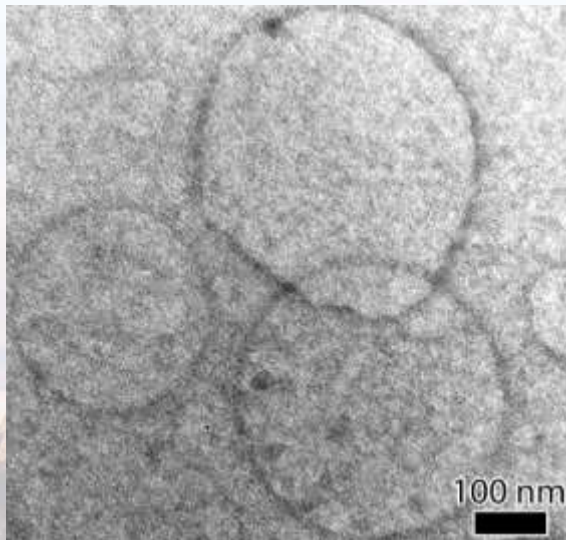
Pitting of nc-Fe due to  
acetic acid corrosion



## Liposomes in Water

S. Hoppe,  
D. Sasaki

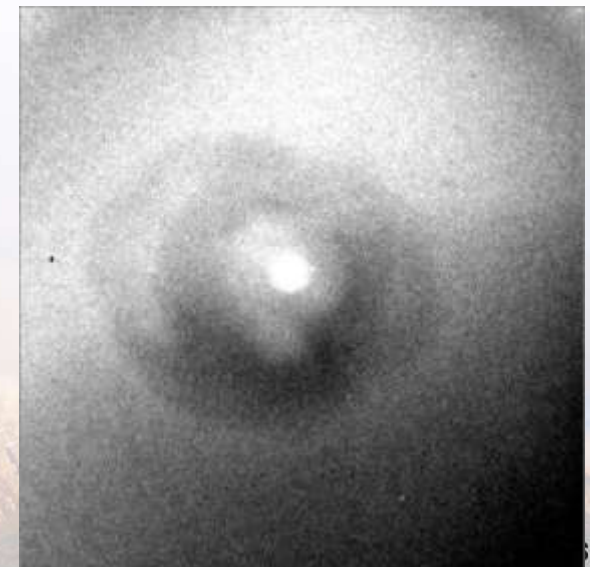
Liposomes  
imaged in  
flowing aqueous  
channel



## La Structure Formation

S. Hoppe,  
T. Nenoff

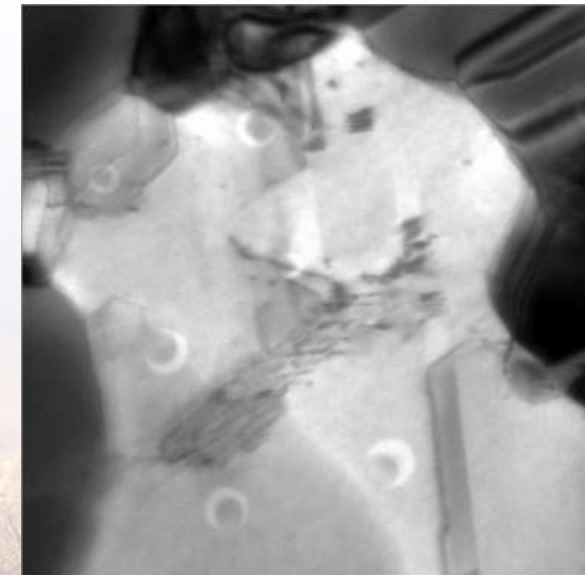
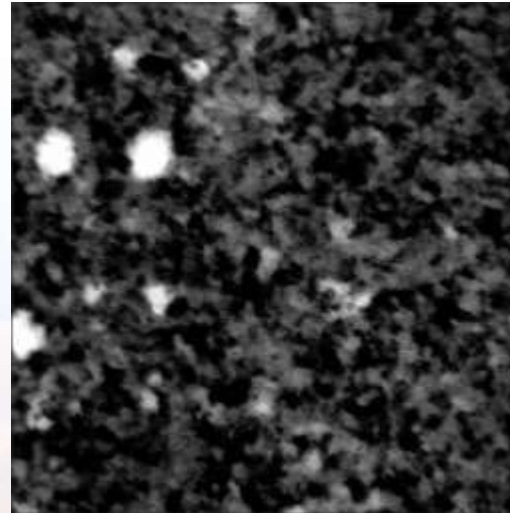
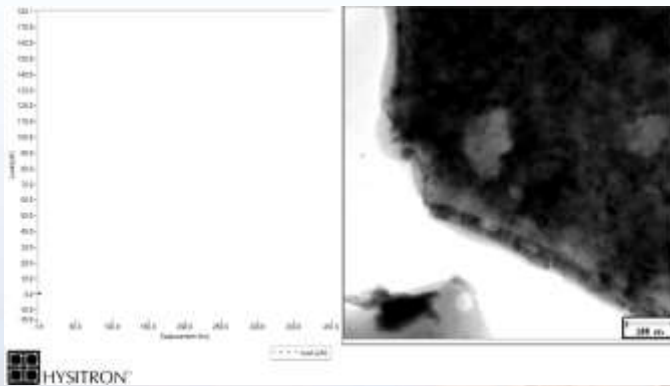
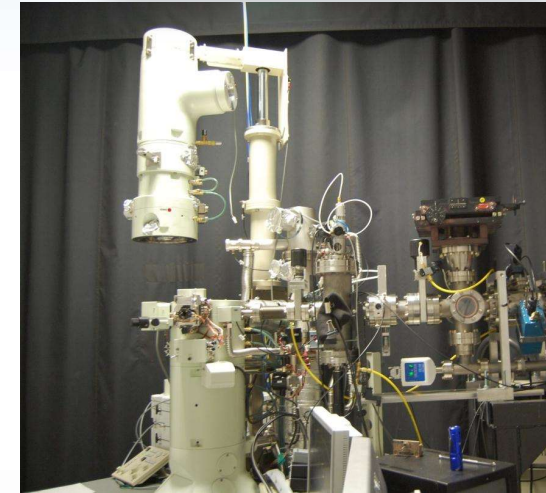
La  
Nanostructure  
form from  $\text{LaCl}_3$   
 $\text{H}_2\text{O}$  in wet cell  
due to beam  
effects



# Summary & Future Interests



- Sandia's I<sup>3</sup>TEM is one of only two facilities in the US
  - Only facility in the world with a wealth of dual *in situ* capabilities
  - *In situ* high energy ion irradiation from H to Au
  - *In situ* gas implantation
  - Eight TEM stages with various capabilities (two beta-testing)
- Apply the current I<sup>3</sup>TEM capabilities to various material systems in combined environmental conditions
- Expand the I<sup>3</sup>TEM capability to include
  - Nano to microsecond imaging
  - Laser heating and/or shock to the sample
  - Addition of precession electron diffraction



**Sandia's I<sup>3</sup>TEM although still under development is providing a wealth of interesting initial observations**



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